

# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

- Direct Upgrades to TL07x and TL08x BiFET Operational Amplifiers
- Faster Slew Rate (20 V/ $\mu$ s Typ) Without Increased Power Consumption
- On-Chip Offset Voltage Trimming for Improved DC Performance and Precision Grades Are Available (1.5 mV, TL051A)
- Available in TSSOP for Small Form-Factor Designs

## description

The TL05x series of JFET-input operational amplifiers offers improved dc and ac characteristics over the TL07x and TL08x families of BiFET operational amplifiers. On-chip zener trimming of offset voltage yields precision grades as low as 1.5 mV (TL051A) for greater accuracy in dc-coupled applications. Texas Instruments improved BiFET process and optimized designs also yield improved bandwidth and slew rate without increased power consumption. The TL05x devices are pin-compatible with the TL07x and TL08x and can be used to upgrade existing circuits or for optimal performance in new designs.

BiFET operational amplifiers offer the inherently higher input impedance of the JFET-input transistors, without sacrificing the output drive associated with bipolar amplifiers. This makes them better suited for interfacing with high-impedance sensors or very low-level ac signals. They also feature inherently better ac response than bipolar or CMOS devices having comparable power consumption.

The TL05x family was designed to offer higher precision and better ac response than the TL08x with the low noise floor of the TL07x. Designers requiring significantly faster ac response or ensured lower noise should consider the Excalibur TLE208x and TLE207x families of BiFET operational amplifiers.

### AVAILABLE OPTIONS

T <sub>A</sub>	V <sub>IOmax</sub> AT 25°C	PACKAGED DEVICES						CHIP FORM‡ (Y)
		SMALL OUTLINE† (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (N)	PLASTIC DIP (P)	
0°C to 70°C	800 $\mu$ V	TL051ACD TL052ACD	—	—	—	—	TL051ACP TL052ACP	TL051Y TL052Y TL054Y
	1.5 mV	TL051CD TL052CD TL054ACD	—	—	—	TL054ACN	TL051CP TL052CP	
	4 mV	TL054CD	—	—	—	TL054CN	—	
–40°C to 85°C	800 $\mu$ V	TL051AID TL052AID	—	—	—	—	TL051AIP TL052AIP	—
	1.5 mV	TL051ID TL052ID TL054AID	—	—	—	TL054AIN	TL051IP TL052IP	
	4 mV	TL054ID	—	—	—	TL054IN	—	
–55°C to 125°C	800 $\mu$ V	TL051AMD TL052AMD	TL051AMFK TL052AMFK	—	TL051AMJG TL052AMJG	—	TL051AMP TL052AMP	—
	1.5 mV	TL051MD TL052MD TL054AMD	TL051MFK TL052MFK TL054AMFK	TL054AMJ	TL051MJG TL052MJG	TL054AMN	TL051MP TL052MP	
	4 mV	TL054MD	TL054MFK	TL054MJ	—	TL054MN	—	

† The D packages are available taped and reeled. Add R suffix to device type (e.g., TL054CDR).

‡ Chip forms are tested at 25°C.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS  
INSTRUMENTS**

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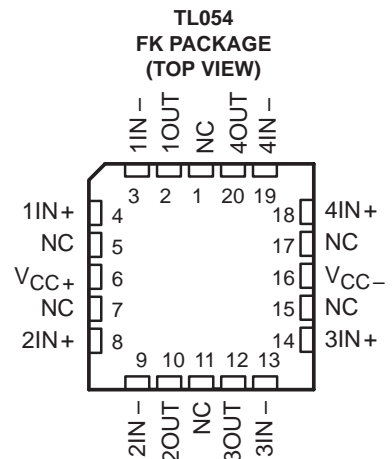
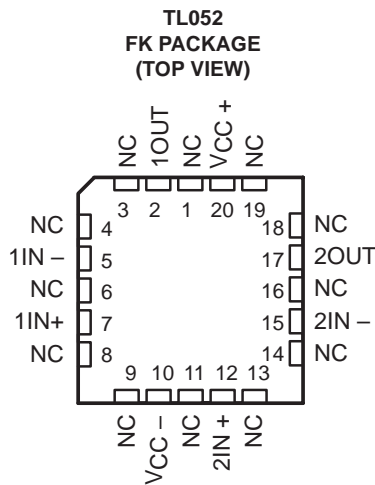
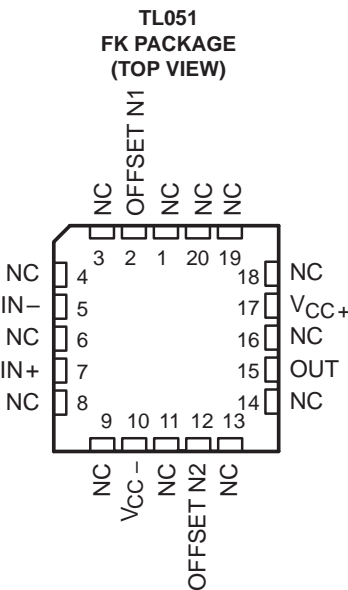
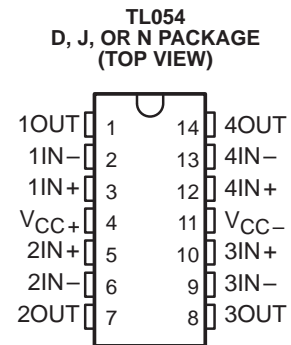
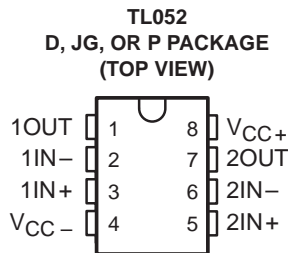
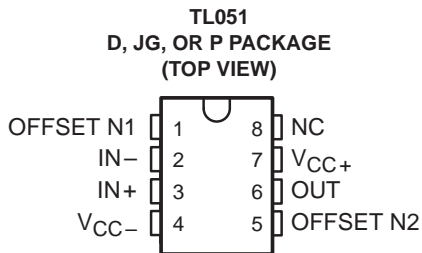
# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## description (continued)

Because BiFET operational amplifiers are designed for use with dual power supplies, care must be taken to observe common-mode input voltage limits and output swing when operating from a single supply. DC biasing of the input signal is required and loads should be terminated to a virtual-ground node at midsupply. Texas Instruments TLE2426 integrated virtual ground generator is useful when operating BiFET amplifiers from single supplies.

The TL05x are fully specified at  $\pm 15$  V and  $\pm 5$  V. For operation in low-voltage and/or single-supply systems, Texas Instruments LinCMOS families of operational amplifiers (TLC-prefix) are recommended. When moving from BiFET to CMOS amplifiers, particular attention should be paid to the slew rate and bandwidth requirements, and also the output loading.

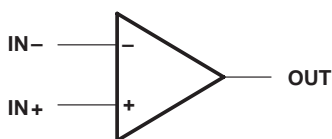


NC – No internal connection

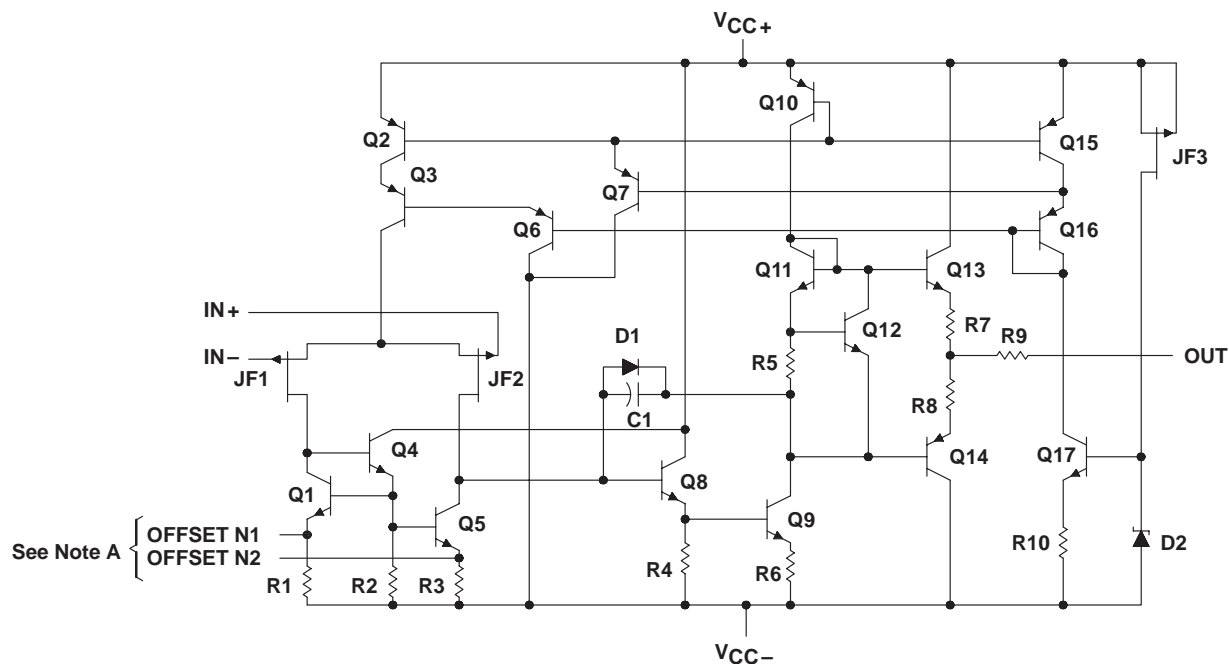
# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

symbol (each amplifier)



equivalent schematic (each amplifier)



NOTE A: OFFSET N1 and OFFSET N2 are only available on the TL051x.

ACTUAL DEVICE COMPONENT COUNT†			
COMPONENT	TL051	TL052	TL054
Transistors	20	34	62
Resistors	10	19	37
Diodes	2	3	5
Capacitors	1	2	4

† These figures include all four amplifiers and all ESD, bias, and trim circuitry.

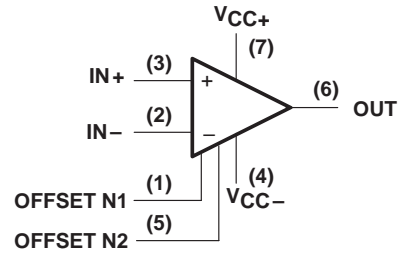
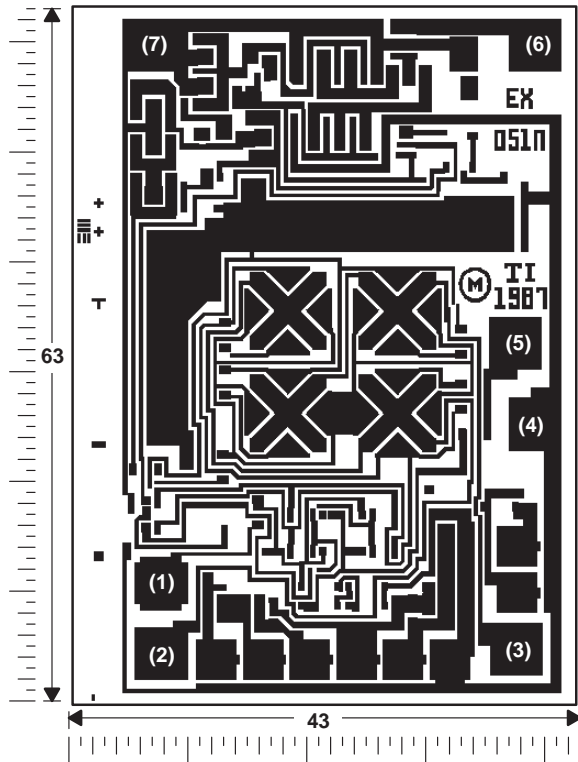
**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL051Y chip information**

This chip, when properly assembled, displays characteristics similar to the TL051. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

**BONDING PAD ASSIGNMENTS**



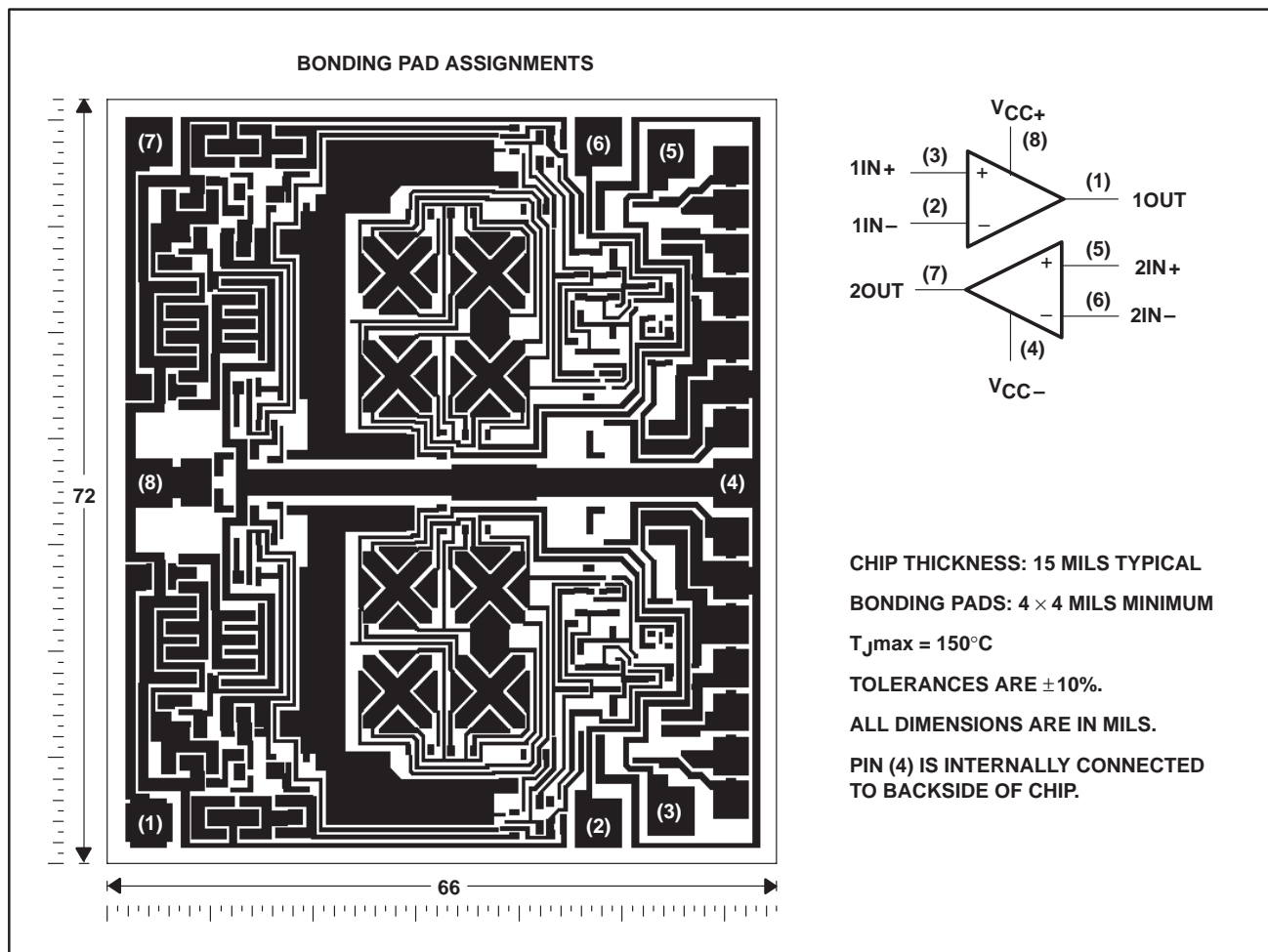
- CHIP THICKNESS: 15 MILS TYPICAL
- BONDING PADS: 4 × 4 MILS MINIMUM
- T<sub>Jmax</sub> = 150°C
- TOLERANCES ARE ±10%.
- ALL DIMENSIONS ARE IN MILS.
- PIN (4) IS INTERNALLY CONNECTED TO BACKSIDE OF CHIP.

# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL052Y chip information

This chip, when properly assembled, displays characteristics similar to the TL052. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

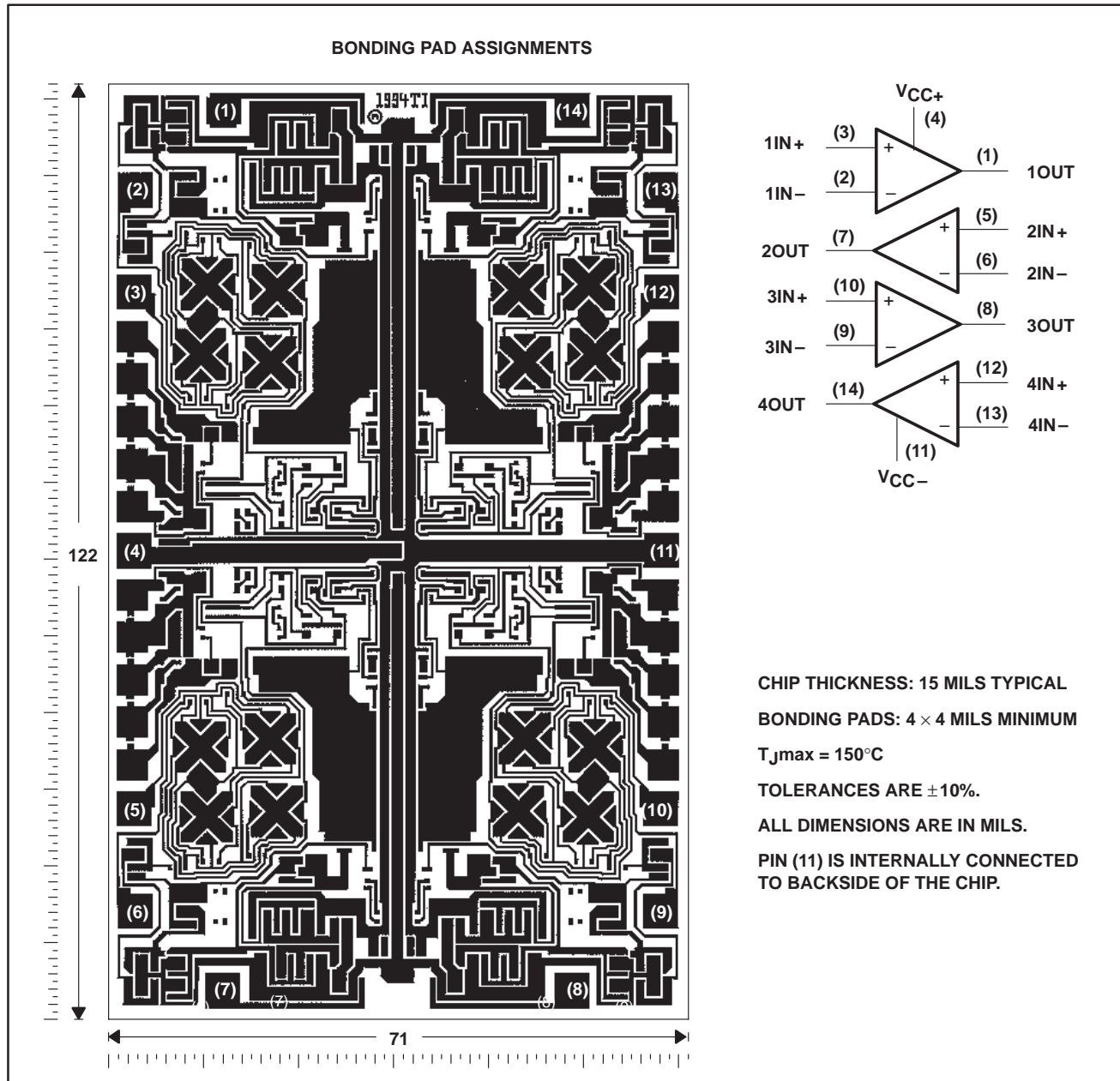


**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL054 chip information**

This chip, when properly assembled, displays characteristics similar to the TL054C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. These chips may be mounted with conductive epoxy or a gold-silicon preform.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, $V_{CC+}$ (see Note 1)	18 V
Supply voltage, $V_{CC-}$ (see Note 1)	–18 V
Differential input voltage (see Note 2)	$\pm 30$ V
Input voltage range, $V_I$ (any input, see Notes 1 and 3)	$\pm 15$ V
Input current, $I_I$ (each input)	$\pm 1$ mA
Output current, $I_O$ (each output)	$\pm 80$ mA
Total current into $V_{CC+}$	160 mA
Total current out of $V_{CC-}$	160 mA
Duration of short-circuit current at (or below) 25°C (see Note 4)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, $T_A$ : C suffix	0°C to 70°C
I suffix	–40°C to 85°C
M suffix	–55°C to 125°C
Storage temperature range	–65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16inch) from case for 10 seconds: D, N, or P package	260°C
Lead temperature 1,6 mm (1/16inch) from case for 60 seconds: J or JG package	300°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. All voltage values, except differential voltages, are with respect to the midpoint between  $V_{CC+}$  and  $V_{CC-}$ .
  2. Differential voltages are at  $IN+$  with respect to  $IN-$ .
  3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
  4. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

**DISSIPATION RATING TABLE**

PACKAGE	$T_A \leq 25^\circ\text{C}$	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$	$T_A = 85^\circ\text{C}$	$T_A = 125^\circ\text{C}$
	POWER RATING		POWER RATING	POWER RATING	POWER RATING
D–8	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW
D–14	950 mW	7.6 mW/°C	608 mW	494 mW	190 mW
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
N	1575 mW	12.6 mW/°C	1008 mW	819 mW	315 mW
P	1000 mW	8.0 mW/°C	640 mW	520 mW	200 mW

## recommended operating conditions

	C SUFFIX		I SUFFIX		M SUFFIX		UNIT
	MIN	MAX	MIN	MAX	MIN	MAX	
Supply voltage, $V_{CC\pm}$	$\pm 5$	$\pm 15$	$\pm 5$	$\pm 15$	$\pm 5$	$\pm 15$	V
Common-mode input voltage, $V_{IC}$	$V_{CC\pm} = \pm 5$ V		–1	4	–1	4	V
	$V_{CC\pm} = \pm 15$ V		–11	11	–11	11	
Operating free-air temperature, $T_A$	0	70	–40	85	–55	125	°C



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL051C and TL051AC electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL051C, TL051AC						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL051C	25°C	0.75	3.5		0.59	1.5	mV
			Full range				4.5	2.5	
		TL051AC	25°C	0.55	2.8		0.35	0.8	
			Full range				3.8	1.8	
α <sub>VIO</sub> Temperature coefficient of input offset voltage‡	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL051C	25°C to 70°C	8		8		μV/°C	
		TL051AC	25°C to 70°C	8		8	25		
Input offset voltage long-term drift§		25°C	0.04		0.04		μV/mo		
I <sub>IO</sub> Input offset current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	4	100	5	100	pA		
		70°C	0.02	1	0.025	1	nA		
I <sub>IB</sub> Input bias current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	20	200	30	200	pA		
		70°C	0.15	4	0.2	4	nA		
V <sub>ICR</sub> Common-mode input voltage range		25°C	-1 to 4	-2.3 to 5.6	-11 to 11	-12.3 to 15.6	V		
		Full range	-1 to 4		-11 to 11				
V <sub>OM+</sub> Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	3	4.2	13	13.9	V		
		Full range	3		13				
	R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8	11.5	12.7			
		Full range	2.5		11.5				
V <sub>OM-</sub> Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	-2.5	-3.5	-12	-13.2	V		
		Full range	-2.5		-12				
	R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2	-11	-12			
		Full range	-2.3		-11				
A <sub>VD</sub> Large-signal differential voltage amplification¶	R <sub>L</sub> = 2 kΩ	25°C	25	59	50	105	V/mV		
		0°C	30	65	60	129			
		70°C	20	46	30	85			
r <sub>i</sub> Input resistance		25°C	10 <sup>12</sup>		10 <sup>12</sup>		Ω		
c <sub>i</sub> Input capacitance		25°C	10		12		pF		
CMRR Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	65	85	75	93	dB		
		0°C	65	84	75	92			
		70°C	65	84	75	91			
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	75	99	75	99	dB		
		0°C	75	98	75	98			
		70°C	75	97	75	97			
I <sub>CC</sub> Supply current	V <sub>O</sub> = 0, No load	25°C	2.6	3.2	2.7	3.2	mA		
		0°C	2.7	3.2	2.8	3.2			
		70°C	2.6	3.2	2.7	3.2			

† Full range is 0°C to 70°C.

‡ This parameter is tested on a sample basis for the TL051A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

§ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V, or for V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



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SLOS178 – FEBRUARY 1997

**TL051C and TL051AC operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL051C, TL051AC						UNIT	
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V				
			MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	16			13 20			V/μs
			Full range	16.4			11 22.6			
SR-	Negative slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	15			13 18			
			Full range	16			11 19.3			
t <sub>r</sub>	Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			56			ns
			0°C	54			55			
			70°C	63			63			
t <sub>f</sub>	Fall time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			57			
			0°C	54			56			
			70°C	62			64			
Overshoot factor		V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	24%			19%			
			0°C	24%			19%			
			70°C	24%			19%			
V <sub>n</sub>	Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	75			75			nV/√Hz
			f = 1 kHz	18			18 30			
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz to 10 kHz	4			4			μV
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz	25°C	0.01			0.01			pA/√Hz
THD	Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ, f = 1 kHz, R <sub>L</sub> = 2 kΩ	25°C	0.003%			0.003%			
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	3			3.1			MHz
			0°C	3.2			3.3			
			70°C	2.7			2.8			
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	59°			62°			
			0°C	58°			62°			
			70°C	59°			62°			

† Full range is 0°C to 70°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis for the TL051A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(rms)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(rms)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL051I and TL051AI electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL051I, TL051AI						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL051I	25°C	0.75	3.5		0.59	1.5	mV
			Full range				5.3	3.3	
		TL051AI	25°C	0.55	2.8		0.35	0.8	
			Full range				4.6	2.6	
α <sub>VIO</sub> Temperature coefficient of input offset voltage‡	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL051I	25°C to 85°C	7		8		μV/°C	
		TL051AI	25°C to 85°C	8		8	25		
Input offset voltage long-term drift§		25°C	0.04		0.04		μV/mo		
I <sub>IO</sub> Input offset current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	4	100	5	100	pA		
		85°C	0.06	10	0.07	10	nA		
I <sub>IB</sub> Input bias current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	20	200	30	200	pA		
		85°C	0.6	20	0.7	20	nA		
V <sub>ICR</sub> Common-mode input voltage range		25°C	-1 to 4	-2.3 to 5.6	-11 to 11	-12.3 to 15.6	V		
	Full range	-1 to 4		-11 to 11					
V <sub>OM+</sub> Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	3	4.2	13	13.9	V		
		Full range	3		13				
	R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8	11.5	12.7			
		Full range	2.5		11.5				
V <sub>OM-</sub> Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	-2.5	-3.5	-12	-13.2	V		
		Full range	-2.5		-12				
	R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2	-11	-12			
		Full range	-2.3		-11				
A <sub>VD</sub> Large-signal differential voltage amplification¶	R <sub>L</sub> = 2 kΩ	25°C	25	59	50	105	V/mV		
		-40°C	30	74	60	145			
		85°C	20	43	30	76			
r <sub>i</sub> Input resistance		25°C	10 <sup>12</sup>		10 <sup>12</sup>		Ω		
c <sub>i</sub> Input capacitance		25°C	10		12		pF		
CMRR Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	65	85	75	93	dB		
		-40°C	65	83	75	90			
		85°C	65	84	75	93			
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	75	99	75	99	dB		
		-40°C	75	98	75	98			
		85°C	75	99	75	99			
I <sub>CC</sub> Supply current	V <sub>O</sub> = 0, No load	25°C	2.6	3.2	2.7	3.2	mA		
		-40°C	2.4	3.2	2.6	3.2			
		85°C	2.5	3.2	2.6	3.2			

† Full range is -40°C to 85°C

‡ This parameter is tested on a sample basis for the TL051A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

§ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V, or for V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL051I and TL051AI operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL051I, TL051AI						UNIT	
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V				
			MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	16			13 20			V/μs
			Full range				11			
SR-	Negative slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	15			13 18			
			Full range				11			
t <sub>r</sub>	Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			56			ns
			-40°C	52			53			
			85°C	64			65			
t <sub>f</sub>	Fall time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			57			
			-40°C	51			53			
			85°C	64			65			
Overshoot factor		V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	24%			19%			
			-40°C	24%			19%			
			85°C	24%			19%			
V <sub>n</sub>	Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	25°C			75			nV/√Hz
			f = 1 kHz	25°C			18 18 30			
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz to 10 kHz	25°C			4			μV
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz	25°C	0.01			0.01			pA/√Hz
THD	Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ, f = 1 kHz, R <sub>L</sub> = 2 kΩ	25°C	0.003%			0.003%			
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	3			3.1			MHz
			-40°C	3.5			3.6			
			85°C	2.6			2.7			
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	59°			62°			
			-40°C	58°			61°			
			85°C	59°			62°			

† Full range is -40°C to 85°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis for the TL051A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(rms)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(rms)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL051M and TL051AM electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL051M, TL051AM						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL051M	25°C	0.75	3.5		0.59	1.5	mV
			Full range				6.5	4.5	
		TL051AM	25°C	0.55	2.8		0.35	0.8	
			Full range				5.8	3.8	
α <sub>VIO</sub> Temperature coefficient of input offset voltage	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL051M	25°C to 125°C	8			8		μV/°C
		TL051AM	25°C to 125°C	8			8		
Input offset voltage long-term drift‡		25°C	0.04			0.04		μV/mo	
I <sub>IO</sub> Input offset current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	4	100		5	100	pA	
		125°C	1	20		2	20	nA	
I <sub>IB</sub> Input bias current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	20	200		30	200	pA	
		125°C	10	50		20	50	nA	
V <sub>ICR</sub> Common-mode input voltage range		25°C	-1 to 4	-2.3 to 5.6		-11 to 11	-12.3 to 15.6	V	
		Full range	-1 to 4			-11 to 11			
V <sub>OM+</sub> Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	3	4.2		13	13.9	V	
		Full range	3			13			
	R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8		11.5	12.7		
		Full range	2.5			11.5			
V <sub>OM-</sub> Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	-2.5	-3.5		-12	-13.2	V	
		Full range	-2.5			-12			
	R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2		-11	-12		
		Full range	-2.3			-11			
A <sub>VD</sub> Large-signal differential voltage amplification§	R <sub>L</sub> = 2 kΩ	25°C	25	59		50	105	V/mV	
		-55°C	30	76		60	149		
		125°C	10	32		15	49		
r <sub>i</sub> Input resistance		25°C	10 <sup>12</sup>			10 <sup>12</sup>		Ω	
c <sub>i</sub> Input capacitance		25°C	10			12		pF	
CMRR Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	65	85		75	93	dB	
		-55°C	65	83		75	92		
		125°C	65	84		75	94		
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	75	99		75	99	dB	
		-55°C	75	98		75	98		
		125°C	75	100		75	100		
I <sub>CC</sub> Supply current	V <sub>O</sub> = 0, No load	25°C	2.6	3.2		2.7	3.2	mA	
		-55°C	2.3	3.2		2.4	3.2		
		125°C	2.4	3.2		2.5	3.2		

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V, or for V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



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**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL051M and TL051AM operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub>	TL051M, TL051AM						UNIT	
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V				
			MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	16			13 20		V/μs	
SR-	Negative slew rate at unity gain†		25°C	15			13			
t <sub>r</sub>	Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			56		ns	
			-55°C	51			52			
			125°C	68			68			
t <sub>f</sub>	Fall time		25°C	55			57			
			-55°C	51			52			
			125°C	68			69			
Overshoot factor			25°C	24%			19%			
			-55°C	25%			19%			
			125°C	25%			19%			
V <sub>n</sub>	Equivalent input noise voltage‡	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	25°C	75			75		nV/√Hz
			f = 1 kHz	25°C	18			19		
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage		f = 10 Hz to 10 kHz	25°C	4			4		μV
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz	25°C	0.01			0.01		pA/√Hz	
THD	Total harmonic distortion§	R <sub>S</sub> = 1 kΩ, f = 1 kHz	R <sub>L</sub> = 2kΩ,	25°C	0.003%			0.003%		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF,	R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	3			3.1		MHz
				-55°C	3.6			3.7		
				125°C	2.3			2.4		
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF,	R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	59°			62°		
				-55°C	57°			61°		
				125°C	59°			62°		

† For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

‡ This parameter is tested on a sample basis for the TL051A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

§ For V<sub>CC±</sub> = ±5 V, V<sub>O(rms)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(rms)</sub> = 6 V.



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL051Y electrical characteristics,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TL051Y						UNIT
		$V_{CC\pm} = \pm 5\text{ V}$			$V_{CC\pm} = \pm 15\text{ V}$			
		MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_O = 0,$ $R_S = 50\ \Omega$ $V_{IC} = 0,$	0.75			0.59			mV
$I_{IO}$ Input offset current	$V_O = 0,$ See Figure 5 $V_{IC} = 0,$	4			5			pA
$I_{IB}$ Input bias current	$V_O = 0,$ See Figure 5 $V_{IC} = 0,$	20			30			pA
$V_{ICR}$ Common-mode input voltage range		-2.3 to 5.6			-12.3 to 15.6			V
$V_{OM+}$ Maximum positive peak output voltage swing	$R_L = 10\ \text{k}\Omega$	4.2			13.9			V
	$R_L = 2\ \text{k}\Omega$	3.8			12.7			
$V_{OM-}$ Maximum negative peak output voltage swing	$R_L = 10\ \text{k}\Omega$	-3.5			-13.2			V
	$R_L = 2\ \text{k}\Omega$	-3.2			-12			
$A_{VD}$ Large-signal differential voltage amplification†	$R_L = 2\ \text{k}\Omega$	59			105			V/mV
$r_i$ Input resistance		$10^{12}$			$10^{12}$			$\Omega$
$c_i$ Input capacitance		10			12			pF
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin},$ $V_O = 0,$ $R_S = 50\ \Omega$	85			93			dB
$k_{SVR}$ Supply-voltage rejection ratio ( $\Delta V_{CC\pm} / \Delta V_{IO}$ )	$V_O = 0,$ $R_S = 50\ \Omega$	99			99			dB
$I_{CC}$ Supply current	$V_O = 0,$ No load	2.6			2.7			mA

† For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_O = \pm 2.3\text{ V}$ , or for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_O = \pm 10\text{ V}$ .



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL051Y operating characteristics,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TL051Y						UNIT		
		$V_{CC\pm} = \pm 5\text{ V}$			$V_{CC\pm} = \pm 15\text{ V}$					
		MIN	TYP	MAX	MIN	TYP	MAX			
SR+	Positive slew rate at unity gain <sup>†</sup>	$R_L = 2\text{ k}\Omega$ , $C_L = 100\text{ pF}$ , See Figure 1	16			20			V/ $\mu\text{s}$	
SR-	Negative slew rate at unity gain <sup>†</sup>		15			18				
$t_r$	Rise time	$V_{I(PP)} = \pm 10\text{ mV}$ , $R_L = 2\text{ k}\Omega$ , $C_L = 100\text{ pF}$ , See Figures 1 and 2	55			56			ns	
$t_f$	Fall time		55			57				
	Overshoot factor		24%			19%				
$V_n$	Equivalent input noise voltage <sup>‡</sup>	$R_S = 20\ \Omega$ , See Figure 3	f = 10 Hz			75			nV/ $\sqrt{\text{Hz}}$	
			f = 1 kHz			18				
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage		f = 10 Hz to 10 kHz			4			$\mu\text{V}$	
$I_n$	Equivalent input noise current		f = 1 kHz			0.01			pA/ $\sqrt{\text{Hz}}$	
THD	Total harmonic distortion <sup>§</sup>	$R_S = 1\text{ k}\Omega$ , f = 1 kHz	$R_L = 2\text{ k}\Omega$			0.003%			0.003%	
$B_1$	Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $C_L = 25\text{ pF}$	$R_L = 2\text{ k}\Omega$ , See Figure 4			3			3.1	MHz
$\phi_m$	Phase margin at unity gain	$V_I = 10\text{ mV}$ , $C_L = 25\text{ pF}$	$R_L = 2\text{ k}\Omega$ , See Figure 4			59°			62°	

<sup>†</sup> For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_{I(PP)} = \pm 1\text{ V}$ ; for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_{I(PP)} = \pm 5\text{ V}$ .

<sup>‡</sup> This parameter is tested on a sample basis for the TL051A. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

<sup>§</sup> For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_{Orms} = 1\text{ V}$ ; for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_{Orms} = 6\text{ V}$ .



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL052C and TL052AC electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS		T <sub>A</sub> †	TL052C, TL052AC						UNIT
				V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL052C	25°C	0.73	3.5	0.65	1.5	mV		
			Full range	4.5			2.5			
		TL052AC	25°C	0.51	2.8	0.4	0.8			
			Full range	3.8			1.8			
α <sub>VIO</sub> Temperature coefficient of input offset voltage‡	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL052C	25°C to 70°C	8			8	μV/°C		
		TL052AC	25°C to 70°C	8			6 25			
Input offset voltage long-term drift§	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	V <sub>IC</sub> = 0,	25°C	0.04			0.04	μV/mo		
I <sub>IO</sub> Input offset current	V <sub>O</sub> = 0, See Figure 5	V <sub>IC</sub> = 0,	25°C	4	100	5	100	pA		
			70°C	0.02	1	0.025	1	nA		
I <sub>IB</sub> Input bias current	V <sub>O</sub> = 0, See Figure 5	V <sub>IC</sub> = 0,	25°C	20	200	30	200	pA		
			70°C	0.15	4	0.2	4	nA		
V <sub>ICR</sub> Common-mode input voltage range			25°C	-1 to 4	-2.3 to 5.6	-11 to 11	-12.3 to 15.6	V		
			Full range	-1 to 4		-11 to 11				
V <sub>OM+</sub> Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ		25°C	3	4.2	13	13.9	V		
			Full range	3			13			
	R <sub>L</sub> = 2 kΩ		25°C	2.5	3.8	11.5	12.7			
			Full range	2.5			11.5			
V <sub>OM-</sub> Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ		25°C	-2.5	-3.5	-12	-13.2	V		
			Full range	-2.5			-12			
	R <sub>L</sub> = 2 kΩ		25°C	-2.3	-3.2	-11	-12			
			Full range	-2.3			-11			
A <sub>VD</sub> Large-signal differential voltage amplification¶	R <sub>L</sub> = 2 kΩ		25°C	25	59	50	105	V/mV		
			0°C	30	65	60	129			
			70°C	20	46	30	85			
r <sub>i</sub> Input resistance			25°C	10 <sup>12</sup>			10 <sup>12</sup>	Ω		
c <sub>i</sub> Input capacitance			25°C	10			12	pF		
CMRR Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0,	R <sub>S</sub> = 50 Ω	25°C	65	85	75	93	dB		
			0°C	65	84	75	92			
			70°C	65	84	75	91			

† Full range is 0°C to 70°C.

‡ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

§ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V; at V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



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**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL052C and TL052AC electrical characteristics at specified free-air temperature (continued)**

PARAMETER	TEST CONDITIONS	T <sub>A</sub>	TL052C, TL052AC						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>O</sub> = 0,    R <sub>S</sub> = 50 Ω	25°C	75	99		75	99	dB	
		0°C	75	98		75	98		
		70°C	75	97		75	97		
I <sub>CC</sub> Supply current (two amplifiers)	V <sub>O</sub> = 0,    No load	25°C		4.6	5.6		4.8	5.6	mA
		0°C		4.7	6.4		4.8	6.4	
		70°C		4.4	6.4		4.6	6.4	
V <sub>O1</sub> /V <sub>O2</sub> Crosstalk attenuation	A <sub>VD</sub> = 100	25°C		120		120		dB	

**TL052C and TL052AC operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL052C, TL052AC						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
SR +    Slew rate at unity gain	R <sub>L</sub> = 2 kΩ,    C <sub>L</sub> = 100 pF, See Figure 1	25°C		17.8		9	20.7	V/μs	
		Full range				8			
25°C			15.4		9	17.8			
Full range					8				
SR –    Negative slew rate at unity gain‡									
t <sub>r</sub> Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C		55		56	ns		
		0°C		54		55			
		70°C		63		63			
t <sub>f</sub> Fall time		25°C		55		57			
		0°C		54		56			
		70°C		62		64			
Overshoot factor		25°C		24%		19%			
		0°C		24%		19%			
		70°C		24%		19%			
V <sub>n</sub> Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz		71		71	nV/√Hz		
		f = 1 kHz		19		19		30	
V <sub>N(PP)</sub> Peak-to-peak equivalent input noise current		f = 10 Hz to 10 kHz		4		4		μV	
I <sub>n</sub> Equivalent input noise current	f = 1 kHz	25°C		0.01		0.01	pA/√Hz		
THD    Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ,    R <sub>L</sub> = 2 kΩ, f = 1 kHz	25°C		0.003%		0.003%			
B <sub>1</sub> Unity-gain bandwidth	V <sub>I</sub> = 10 mV,    R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 25 pF,    See Figure 4	25°C		3		3	MHz		
		0°C		3.2		3.2			
		70°C		2.6		2.7			
φ <sub>m</sub> Phase margin at unity gain	V <sub>I</sub> = 10 mV,    R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 25 pF,    See Figure 4	25°C		60°		63°			
		0°C		59°		63°			
		70°C		60°		63°			

† Full range is 0°C to 70°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(RMS)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(RMS)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL052I and TL052AI electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS		T <sub>A</sub> †	TL052I, TL052AI						UNIT
				V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage		TL052I	25°C	0.73	3.5		0.65	1.5	mV	
			Full range				5.3	3.3		
			TL052AI	25°C	0.51	2.8		0.4		0.8
				Full range				4.6		2.6
α <sub>VIO</sub> Temperature coefficient‡		TL052I	25°C to 85°C	7		6		μV/°C		
			TL052AI	25°C to 85°C	6		6 25			
Input offset voltage long-term drift§	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	V <sub>IC</sub> = 0,	25°C	0.04		0.04		μV/mo		
I <sub>IO</sub> Input offset current	V <sub>O</sub> = 0, See Figure 5	V <sub>IC</sub> = 0,	25°C	4	100		5	100	pA	
			85°C	0.06	10		0.07	10	nA	
I <sub>IB</sub> Input bias current	V <sub>O</sub> = 0, See Figure 5	V <sub>IC</sub> = 0,	25°C	20	200		30	200	pA	
			85°C	0.6	20		0.7	20	nA	
V <sub>ICR</sub> Common-mode input voltage range			25°C	-1 to 4	-2.3 to 5.6		-11 to 11	-12.3 to 15.6	V	
			Full range	-1 to 4			-11 to 11			
V <sub>OM+</sub> Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ		25°C	3	4.2		13	13.9	V	
			Full range	3			13			
	R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8		11.5	12.7			
		Full range	2.5			11.5				
V <sub>OM-</sub> Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ		25°C	-2.5	-3.5		-12	-13.2	V	
			Full range	-2.5			-12			
	R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2		-11	-12			
		Full range	-2.3			-11				
A <sub>VD</sub> Large-signal differential voltage amplification¶	R <sub>L</sub> = 2 kΩ		25°C	25	59		50	105	V/mV	
			-40°C	30	74		60	145		
			85°C	20	43		30	76		
r <sub>i</sub> Input resistance			25°C	10 <sup>12</sup>		10 <sup>12</sup>		Ω		
c <sub>i</sub> Input capacitance			25°C	10		12		pF		
CMRR Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω		25°C	65	85		75	93	dB	
			-40°C	65	83		75	90		
			85°C	65	84		75	93		

† Full range is -40°C to 85°C.

‡ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters

§ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

¶ At V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V; at V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL052I and TL052AI electrical characteristics at specified free-air temperature (continued)**

PARAMETER	TEST CONDITIONS	T <sub>A</sub>	TL052I, TL052AI						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>O</sub> = 0,    R <sub>S</sub> = 50 Ω	25°C	75	99		75	99	dB	
		-40°C	75	98		75	98		
		85°C	75	99		75	99		
I <sub>CC</sub> Supply current (two amplifiers)	V <sub>O</sub> = 0,    No load	25°C		4.6	5.6		4.8	5.6	mA
		-40°C		4.5	6.4		4.7	6.4	
		85°C		4.4	6.4		4.6	6.4	
V <sub>O1</sub> /V <sub>O2</sub> Crosstalk attenuation	A <sub>VD</sub> = 100	25°C		120		120		dB	

**TL052I and TL052AI operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL052I, TL052AI						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
SR +    Slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ,    C <sub>L</sub> = 100 pF, See Figure 1	25°C		17.8		9	20.7	V/μs	
		Full range				8			
SR -    Negative slew rate at unity gain‡		25°C		15.4		9	17.8		
		Full range				8			
t <sub>r</sub> Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ,    C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C		55		56	ns		
		-40°C		52		53			
		85°C		64		65			
t <sub>f</sub> Fall time		25°C		55		57			
		-40°C		51		53			
		85°C		64		65			
Overshoot factor		25°C		24%		19%			
		-40°C		24%		19%			
		85°C		24%		19%			
V <sub>n</sub> Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	25°C		71		71		
		f = 1 kHz	25°C		19		19		30
V <sub>N(PP)</sub> Peak-to-peak equivalent input noise current		f = 10 Hz to 10 kHz	25°C		4		4		μV
	I <sub>n</sub> Equivalent input noise current	f = 1 kHz	25°C		0.01		0.01	pA/√Hz	
THD    Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ,    R <sub>L</sub> = 2 kΩ, f = 1 kHz	25°C		0.003%		0.003%			
B <sub>1</sub> Unity-gain bandwidth	V <sub>I</sub> = 10 mV,    R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 25 pF,    See Figure 4	25°C		3		3	MHz		
		-40°C		3.5		3.6			
		85°C		2.5		2.6			
φ <sub>m</sub> Phase margin at unity gain	V <sub>I</sub> = 10 mV,    R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 25 pF,    See Figure 4	25°C		60°		63°			
		-40°C		58°		61°			
		85°C		60°		63°			

† Full range is -40°C to 85°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(RMS)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(RMS)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL052M and TL052AM electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL052M, TL052AM						UNIT
			V <sub>CC±</sub> = ± 5 V			V <sub>CC±</sub> = ± 15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub>	Input offset voltage	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, R <sub>S</sub> = 50 Ω	TL052M	25°C	0.73	3.5	0.65	1.5	mV
				Full range	6.5		4.5		
			TL052AM	25°C	0.51	2.8	0.4	0.8	
				Full range	5.8		3.8		
α <sub>VIO</sub>	Temperature coefficient of input offset voltage	TL052M	25°C to 125°C	10		9		μV/°C	
			TL052AM	25°C to 125°C	9		8		
	Input offset voltage long-term drift‡	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	V <sub>IC</sub> = 0, 25°C	0.04		0.04		μV/mo	
I <sub>IO</sub>	Input offset current	V <sub>O</sub> = 0, See Figure 5	V <sub>IC</sub> = 0, 25°C	25°C	4	100	5	100	pA
				125°C	1	20	2	20	nA
I <sub>IB</sub>	Input bias current	V <sub>O</sub> = 0, See Figure 5	V <sub>IC</sub> = 0, 25°C	25°C	20	200	30	200	pA
				125°C	10	50	20	50	nA
V <sub>ICR</sub>	Common-mode input voltage range		25°C	-1 to 4	-2.3 to 5.6	-11 to 11	-12.3 to 15.6	V	
				Full range	-1 to 4	-11 to 11			
V <sub>OM+</sub>	Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	3	4.2	13	13.9	V	
			Full range	3		13			
		R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8	11.5	12.7		
			Full range	2.5		11.5			
V <sub>OM-</sub>	Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	-2.5	-3.5	-12	-13.2	V	
			Full range	-2.5		-12			
		R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2	-11	-12		
			Full range	-2.3		-11			
A <sub>VD</sub>	Large-signal differential voltage amplification§	R <sub>L</sub> = 2 kΩ	25°C	25	59	50	105	V/mV	
			-55°C	30	76	60	149		
			125°C	10	32	15	49		
r <sub>i</sub>	Input resistance		25°C	10 <sup>12</sup>		10 <sup>12</sup>		Ω	
c <sub>i</sub>	Input capacitance		25°C	10		12		pF	
CMRR	Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	65	85	75	93	dB	
			-55°C	65	83	75	92		
			125°C	65	84	75	94		
k <sub>SVR</sub>	Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	75	99	75	99	dB	
			-55°C	75	98	75	98		
			125°C	75	100	75	100		
I <sub>CC</sub>	Supply current (two amplifiers)	V <sub>O</sub> = 0, No load	25°C	4.6	5.6	4.8	5.6	mA	
			-55°C	4.4	6.4	4.5	6.4		
			125°C	4.2	6.4	4.4	6.4		
V <sub>O1</sub> /V <sub>O2</sub>	Crosstalk attenuation	A <sub>VD</sub> = 100	25°C	120		120		dB	

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ For V<sub>CC±</sub> = ± 5 V, V<sub>O</sub> = ± 2.3 V; at V<sub>CC±</sub> = ± 15 V, V<sub>O</sub> = ± 10 V.



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL052M and TL052AM operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL052M, TL052AM						UNIT		
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V					
			MIN	TYP	MAX	MIN	TYP	MAX			
SR +	Positive slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	17.8			9 20.7			V/μs	
			Full range				8				
SR –	Negative slew rate at unity gain‡	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1	25°C	15.4			9 17.8				
			Full range				8				
t <sub>r</sub>	Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			56			ns	
			–55°C	51			52				
			125°C	68			68				
t <sub>f</sub>	Fall time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			57				
			–55°C	51			52				
			125°C	68			69				
Overshoot factor		V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	24%			19%				
			–55°C	25%			19%				
			125°C	25%			19%				
V <sub>n</sub>	Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	25°C			71			nV/√Hz	
			f = 1 kHz	25°C			19				
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise current	f = 10 Hz to 10 kHz	25°C	4			4			μV	
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz	25°C	0.01			0.01			pA/√Hz	
THD	Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ, f = 1 kHz	R <sub>L</sub> = 2 kΩ,	25°C	0.003%			0.003%			
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF,	R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	3			3			MHz
				–55°C	3.6			3.7			
				125°C	2.3			2.4			
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF,	R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	60°			63°			
				–55°C	57°			61°			
				125°C	60°			63°			

† Full range is –55°C to 125°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(RMS)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(RMS)</sub> = 6 V.



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL052Y electrical characteristics,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TL052Y						UNIT		
		$V_{CC\pm} = \pm 5\text{ V}$			$V_{CC\pm} = \pm 15\text{ V}$					
		MIN	TYP	MAX	MIN	TYP	MAX			
$V_{IO}$	Input offset voltage	$V_O = 0,$ $R_S = 50\ \Omega$	$V_{IC} = 0,$	0.73			0.65			mV
	Input offset voltage long-term drift			0.04			0.04			$\mu\text{V}/\text{mo}$
$I_{IO}$	Input offset current	$V_O = 0,$ See Figure 5	$V_{IC} = 0,$	4			5			pA
$I_{IB}$	Input bias current	$V_O = 0,$ See Figure 5	$V_{IC} = 0,$	20			30			pA
$V_{ICR}$	Common-mode input voltage range			-2.3 to 5.6			-12.3 to 15.6			V
$V_{OM+}$	Maximum positive peak output voltage swing	$R_L = 10\ \text{k}\Omega$		4.2			13.9			V
		$R_L = 2\ \text{k}\Omega$		3.8			12.7			
$V_{OM-}$	Maximum negative peak output voltage swing	$R_L = 10\ \text{k}\Omega$		-3.5			-13.2			
		$R_L = 2\ \text{k}\Omega$		-3.2			-12			
$A_{VD}$	Large-signal differential voltage amplification†	$R_L = 2\ \text{k}\Omega$		59			105			V/mV
$r_i$	Input resistance			$10^{12}$			$10^{12}$			$\Omega$
$c_i$	Input capacitance			10			12			pF
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICRmin},$	$R_S = 50\ \Omega$	85			93			dB
$k_{SVR}$	Supply-voltage rejection ratio ( $\Delta V_{CC\pm} / \Delta V_{IO}$ )	$V_O = 0,$	$R_S = 50\ \Omega$	99			99			dB
$I_{CC}$	Supply current (two amplifiers)	$V_O = 0,$	No load	4.6			4.8			mA
$V_{O1}/V_{O2}$	Crosstalk attenuation	$A_{VD} = 100$		120			120			dB

† For  $V_{CC\pm} = \pm 5\text{ V}, V_O = \pm 2.3\text{ V};$  at  $V_{CC\pm} = \pm 15\text{ V}, V_O = \pm 10\text{ V}.$

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL052Y operating characteristics,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TL052Y						UNIT		
		$V_{CC\pm} = \pm 5\text{ V}$			$V_{CC\pm} = \pm 15\text{ V}$					
		MIN	TYP	MAX	MIN	TYP	MAX			
SR +	Positive slew rate at unity gain <sup>†</sup>	$R_L = 2\text{ k}\Omega$ , See Figure 1		$C_L = 100\text{ pF}$		17.8		20.7		V/ $\mu\text{s}$
SR –	Negative slew rate at unity gain <sup>†</sup>					15.4		17.8		
$t_r$	Rise time	$V_{I(PP)} = \pm 10\text{ mV}$ , $R_L = 2\text{ k}\Omega$ , See Figures 1 and 2		$C_L = 100\text{ pF}$		55		56		ns
$t_f$	Fall time					55		57		
	Overshoot factor					24%		19%		
$V_n$	Equivalent input noise voltage <sup>‡</sup>	$R_S = 20\ \Omega$ , See Figure 3	f = 10 Hz		71		71		nV/ $\sqrt{\text{Hz}}$	
			f = 1 kHz		19		19			
$V_{N(PP)}$	Peak-to-peak equivalent input noise current		f = 10 Hz to 10 kHz		4		4			$\mu\text{V}$
$I_n$	Equivalent input noise current	f = 1 kHz		0.01		0.01		pA/ $\sqrt{\text{Hz}}$		
THD	Total harmonic distortion <sup>§</sup>	$R_S = 1\text{ k}\Omega$ , f = 1 kHz	$R_L = 2\text{ k}\Omega$		0.003%		0.003%			
$B_1$	Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $C_L = 25\text{ pF}$ ,	$R_L = 2\text{ k}\Omega$ , See Figure 4		3		3		MHz	
$\phi_m$	Phase margin at unity gain	$V_I = 10\text{ mV}$ , $C_L = 25\text{ pF}$ ,	$R_L = 2\text{ k}\Omega$ , See Figure 4		60°		63°			

<sup>†</sup> This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

<sup>‡</sup> For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_{I(PP)} = \pm 1\text{ V}$ ; for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_{I(PP)} = \pm 5\text{ V}$ .

<sup>§</sup> For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_{O(RMS)} = 1\text{ V}$ ; for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_{O(RMS)} = 6\text{ V}$ .



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL054C and TL054AC electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL054C, TL054AC						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub>	Input offset voltage	25°C	TL054C			TL054AC			mV
			25°C			25°C			
			Full range			Full range			
			25°C			25°C			
αV <sub>IO</sub>	Temperature coefficient of input offset voltage	25°C to 70°C	TL054C			TL054AC			μV/°C
			25°C			25°C			
			Full range			Full range			
			25°C to 70°C			25°C to 70°C			
Input offset voltage long-term drift‡		25°C	0.04			0.04			μV/mo
I <sub>IO</sub>	Input offset current	25°C	4			5			pA
		70°C	0.02			0.025			nA
I <sub>IB</sub>	Input bias current	25°C	20			30			pA
		70°C	0.15			0.2			nA
V <sub>ICR</sub>	Common-mode input voltage range	25°C	-1 to 4			-11 to 11			V
		Full range	-1 to 4			-11 to 11			
V <sub>OM+</sub>	Maximum positive peak output voltage swing	25°C	R <sub>L</sub> = 10 kΩ			R <sub>L</sub> = 10 kΩ			V
			Full range			Full range			
		25°C	R <sub>L</sub> = 2 kΩ			R <sub>L</sub> = 2 kΩ			
			Full range			Full range			
V <sub>OM-</sub>	Maximum negative peak output voltage swing	25°C	R <sub>L</sub> = 10 kΩ			R <sub>L</sub> = 10 kΩ			V
			Full range			Full range			
		25°C	R <sub>L</sub> = 2 kΩ			R <sub>L</sub> = 2 kΩ			
			Full range			Full range			
A <sub>VD</sub>	Large-signal differential voltage amplification§	25°C	25			50			V/mV
		0°C	30			60			
		70°C	20			30			
r <sub>i</sub>	Input resistance	25°C	10 <sup>12</sup>			10 <sup>12</sup>			Ω
c <sub>i</sub>	Input capacitance	25°C	10			12			pF
CMRR	Common-mode rejection ratio	25°C	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω			V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω			dB
			0°C			0°C			
			70°C			70°C			
k <sub>SVR</sub>	Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	25°C	V <sub>CC±</sub> = ±5 V to ±15 V, V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω			V <sub>CC±</sub> = ±5 V to ±15 V, V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω			dB
			0°C			0°C			
			70°C			70°C			
I <sub>CC</sub>	Supply current (four amplifiers)	25°C	8.1			8.4			mA
		0°C	8.2			8.5			
		70°C	7.9			8.2			
V <sub>O1</sub> /V <sub>O2</sub>	Crosstalk attenuation	25°C	120			120			dB

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V, at V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.B





**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL054C and TL054AC operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL054C, TL054AC						UNIT	
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V				
			MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain	R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figure 1 and Note 7	25°C	15.4			10 17.8			V/μs
			0°C	15.7			8 17.9			
SR-	Negative slew rate at unity gain‡		70°C	14.4			8 17.5			
			25°C	13.9			10 15.9			
			0°C	14.3			8 16.1			
			70°C	13.3			8 15.5			
t <sub>r</sub>	Rise time	V <sub>I(PP)</sub> = ±10 mV, R <sub>L</sub> = 2 kΩ, C <sub>L</sub> = 100 pF, See Figures 1 and 2	25°C	55			56			ns
			0°C	54			55			
			70°C	63			63			
t <sub>f</sub>	Fall time		25°C	55			57			
			0°C	54			56			
			70°C	62			64			
	Overshoot factor		25°C	24%			19%			
			0°C	24%			19%			
			70°C	24%			19%			
V <sub>n</sub>	Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	25°C			75			nV/√Hz
			f = 1 kHz	25°C			21 45			
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage		f = 10 Hz to 10 kHz	25°C			4			
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz	25°C			0.01			pA/√Hz	
THD	Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ, f = 1 kHz	25°C			0.003%				
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	2.7			2.7			MHz
			0°C	3			3			
			70°C	2.4			2.4			
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	61°			64°			
			0°C	60°			64°			
			70°C	61°			63°			

† Full range is 0°C to 70°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(rms)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(rms)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL054I and TL054AI electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL054I, TL054AI						UNIT	
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V				
			MIN	TYP	MAX	MIN	TYP	MAX		
V <sub>IO</sub>	Input offset voltage	TL054I	25°C	0.64	5.5		0.56	4	mV	
			Full range			8.8		7.3		
			TL054AI	25°C	0.57	3.5		0.5		1.5
				Full range			6.8			4.8
αV <sub>IO</sub>	Temperature coefficient of input offset voltage	TL054I	25°C to 85°C	25		24		μV/°C		
			TL054AI	25°C to 85°C	25		23			
	Input offset voltage long-term drift‡		25°C	0.04		0.04		μV/mo		
I <sub>IO</sub>	Input offset current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	4	100		5	100	pA	
			85°C	0.06	10		0.07	10	nA	
I <sub>IB</sub>	Input bias current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	20	200		30	200	pA	
			85°C	0.6	20		0.7	20	nA	
V <sub>ICR</sub>	Common-mode input voltage range		25°C	-1 to 4	-2.3 to 5.6		-11 to 11	-12.3 to 15.6	V	
			Full range	-1 to 4			-11 to 11			
V <sub>OM+</sub>	Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	3	4.2		13	13.9	V	
			Full range	3			13			
		R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8		11.5	12.7		
			Full range	2.5			11.5			
V <sub>OM-</sub>	Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	-2.5	-3.5		-12	-13.2	V	
			Full range	-2.5			-12			
		R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2		-11	-12		
			Full range	-2.3			-11			
A <sub>VD</sub>	Large-signal differential voltage amplification§	R <sub>L</sub> = 2 kΩ	25°C	25	72		50	133	V/mV	
			-40°C	30	101		60	212		
			85°C	20	50		30	70		
r <sub>i</sub>	Input resistance		25°C	10 <sup>12</sup>		10 <sup>12</sup>		Ω		
c <sub>i</sub>	Input capacitance		25°C	10		12		pF		
CMRR	Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	65	84		75	92	dB	
			-40°C	65	83		75	92		
			85°C	65	84		75	93		
k <sub>SVR</sub>	Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>CC±</sub> = ±5 V to ±15 V, V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	75	99		75	99	dB	
			-40°C	75	98		75	99		
			85°C	75	99		75	99		
I <sub>CC</sub>	Supply current (four amplifiers)	V <sub>O</sub> = 0, No load	25°C	8.1	11.2		8.4	11.2	mA	
			-40°C	7.9	12.8		8.2	12.8		
			85°C	7.6	11.2		7.9	11.2		
V <sub>O1</sub> /V <sub>O2</sub>	Crosstalk attenuation	A <sub>VD</sub> = 100	25°C	120		120		dB		

† Full range is -40°C to 85°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V, at V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL054I and TL054AI operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL054I, TL054AI						UNIT	
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V				
			MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain	25°C	15.4			10 17.8			V/μs	
		-40°C	16.4			8 18				
		85°C	14			8 17.3				
SR-	Negative slew rate at unity gain‡	25°C	13.9			10 15.9				
		-40°C	14.7			8 16.1				
		85°C	13			8 15.3				
t <sub>r</sub>	Rise time	25°C	55			56			ns	
		-40°C	52			53				
		85°C	64			65				
t <sub>f</sub>	Fall time	25°C	55			57				
		-40°C	51			53				
		85°C	64			65				
	Overshoot factor	25°C	24%			19%				
		-40°C	24%			19%				
		85°C	24%			19%				
V <sub>n</sub>	Equivalent input noise voltage§	f = 10 Hz	25°C	75			75			nV/√Hz
		f = 1 kHz	25°C	21			21 45			
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	f = 10 Hz to 10 kHz	25°C	4			4			μV
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz	25°C	0.01			0.01			pA/√Hz
THD	Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ, f = 1 kHz, R <sub>L</sub> = 2 kΩ	25°C	0.003%			0.003%			
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	2.7			2.7			MHz
			-40°C	3.3			3.3			
			85°C	2.3			2.4			
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF, R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	61°			64°			
			-40°C	59°			62°			
			85°C	61°			64°			

† Full range is -40°C to 85°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(rms)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(rms)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL054M and TL054AM electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL054M, TL054AM						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub>	Input offset voltage	TL054M	25°C	0.64	5.5	0.56	4	mV	
			Full range	10.5			9		
			TL054AM	25°C	0.57	3.5	0.5		1.5
				Full range	8.5				6.5
αV <sub>IO</sub>	Temperature coefficient of input offset voltage	TL054M	25°C to 85°C	21		20		μV/°C	
			TL054AM	25°C to 85°C	21		20		
	Input offset voltage long-term drift‡		25°C	0.04		0.04		μV/mo	
I <sub>IO</sub>	Input offset current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	4	100	5	100	pA	
			125°C	1	20	2	20	nA	
I <sub>IB</sub>	Input bias current	V <sub>O</sub> = 0, V <sub>IC</sub> = 0, See Figure 5	25°C	20	200	30	200	pA	
			125°C	10	50	20	50	nA	
V <sub>ICR</sub>	Common-mode input voltage range		25°C	-1 to 4	-2.3 to 5.6	-11 to 11	-12.3 to 15.6	V	
			Full range	-1 to 4		-11 to 11			
V <sub>OM+</sub>	Maximum positive peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	3	4.2	13	13.9	V	
			Full range	3		13			
		R <sub>L</sub> = 2 kΩ	25°C	2.5	3.8	11.5	12.7		
			Full range	2.5		11.5			
V <sub>OM-</sub>	Maximum negative peak output voltage swing	R <sub>L</sub> = 10 kΩ	25°C	-2.5	-3.5	-12	-13.2	V	
			Full range	-2.5		-12			
		R <sub>L</sub> = 2 kΩ	25°C	-2.3	-3.2	-11	-12		
			Full range	-2.3		-11			
A <sub>VD</sub>	Large-signal differential voltage amplification§	R <sub>L</sub> = 2 kΩ	25°C	25	72	50	133	V/mV	
			-55°C	30	99	60	209		
			125°C	10	35	15	35		
r <sub>i</sub>	Input resistance		25°C	10 <sup>12</sup>		10 <sup>12</sup>		Ω	
c <sub>i</sub>	Input capacitance		25°C	10		12		pF	
CMRR	Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICRmin</sub> , V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	65	84	75	92	dB	
			-55°C	65	83	75	92		
			125°C	65	84	75	93		
k <sub>SVR</sub>	Supply-voltage rejection ratio (ΔV <sub>CC±</sub> /ΔV <sub>IO</sub> )	V <sub>CC±</sub> = ±5 V to ±15 V, V <sub>O</sub> = 0, R <sub>S</sub> = 50 Ω	25°C	75	99	75	99	dB	
			-40°C	75	98	75	98		
			85°C	75	100	75	100		
I <sub>CC</sub>	Supply current (four amplifiers)	V <sub>O</sub> = 0, No load	25°C	8.1	11.2	8.4	11.2	mA	
			-55°C	7.8	12.8	8.1	12.8		
			125°C	7.1	11.2	7.5	11.2		
V <sub>O1</sub> /V <sub>O2</sub>	Crosstalk attenuation	A <sub>VD</sub> = 100	25°C	120		120		dB	

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T<sub>A</sub> = 150°C extrapolated to T<sub>A</sub> = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ For V<sub>CC±</sub> = ±5 V, V<sub>O</sub> = ±2.3 V, at V<sub>CC±</sub> = ±15 V, V<sub>O</sub> = ±10 V.



**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL054M and TL054AM operating characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TL054M, TL054AM						UNIT
			V <sub>CC±</sub> = ±5 V			V <sub>CC±</sub> = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain	25°C	15.4			10 17.8			V/μs
SR-	Negative slew rate at unity gain‡	-55°C	16.7			18.3			
		125°C	12.9			16.7			
		25°C	13.9			10 15.9			
		-55°C	14.7			16.3			
		125°C	12.2			14.5			
t <sub>r</sub>	Rise time	25°C	55			56			ns
t <sub>f</sub>	Fall time	-55°C	51			52			
		125°C	68			68			
		25°C	55			57			
		-55°C	51			52			
		125°C	68			69			
	Overshoot factor	25°C	24%			19%			
		-55°C	25%			19%			
		125°C	25%			19%			
V <sub>n</sub>	Equivalent input noise voltage§	R <sub>S</sub> = 20 Ω, See Figure 3	f = 10 Hz	25°C	75			nV/√Hz	
			f = 1 kHz	25°C	21 45				
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage		f = 10 Hz to 10 kHz	25°C	4			μV	
I <sub>n</sub>	Equivalent input noise current	f = 1 kHz		25°C	0.01			pA/√Hz	
THD	Total harmonic distortion¶	R <sub>S</sub> = 1 kΩ, f = 1 kHz	R <sub>L</sub> = 2 kΩ,	25°C	0.003%				
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF,	R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	2.7			MHz	
				-55°C	3.4				
				125°C	2.1				
φ <sub>m</sub>	Phase margin at unity gain	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 25 pF,	R <sub>L</sub> = 2 kΩ, See Figure 4	25°C	61°				
				-55°C	58°				
				125°C	60°				

† Full range is -55°C to 125°C.

‡ For V<sub>CC±</sub> = ±5 V, V<sub>I(PP)</sub> = ±1 V; for V<sub>CC±</sub> = ±15 V, V<sub>I(PP)</sub> = ±5 V.

§ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

¶ For V<sub>CC±</sub> = ±5 V, V<sub>O(rms)</sub> = 1 V; for V<sub>CC±</sub> = ±15 V, V<sub>O(rms)</sub> = 6 V.



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## TL054Y electrical characteristics, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TL054Y						UNIT		
		$V_{CC\pm} = \pm 5\text{ V}$			$V_{CC\pm} = \pm 15\text{ V}$					
		MIN	TYP	MAX	MIN	TYP	MAX			
$V_{IO}$	Input offset voltage	$V_O = 0,$ $R_S = 50\ \Omega$		$V_{IC} = 0,$		0.64		0.56		mV
$I_{IO}$	Input offset current	$V_O = 0,$ See Figure 5		$V_{IC} = 0,$		4		5		pA
$I_{IB}$	Input bias current	$V_O = 0,$ See Figure 5		$V_{IC} = 0,$		20		30		pA
$V_{ICR}$	Common-mode input voltage range			-2.3 to 5.6		-12.3 to 15.6				V
$V_{OM+}$	Maximum positive peak output voltage swing	$R_L = 10\ \text{k}\Omega$		4.2		13.9				V
		$R_L = 2\ \text{k}\Omega$		3.8		12.7				
$V_{OM-}$	Maximum negative peak output voltage swing	$R_L = 10\ \text{k}\Omega$		-3.5		-13.2				V
		$R_L = 2\ \text{k}\Omega$		-3.2		-12				
$A_{VD}$	Large-signal differential voltage amplification†	$R_L = 2\ \text{k}\Omega,$		72		133				V/mV
$r_i$	Input resistance			$10^{12}$		$10^{12}$				$\Omega$
$c_i$	Input capacitance			10		12				pF
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICRmin},$ $V_O = 0,$ $R_S = 50\ \Omega$		84		92				dB
$k_{SVR}$	Supply-voltage rejection ratio ( $\Delta V_{CC\pm} / \Delta V_{IO}$ )	$V_{CC\pm} = \pm 5\text{ V to } \pm 15\text{ V},$ $V_O = 0,$ $R_S = 50\ \Omega$		99		99				dB
$I_{CC}$	Supply current (four amplifiers)	$V_O = 0,$ No load		8.1		8.4				mA
$V_{O1}/V_{O2}$	Crosstalk attenuation	$A_{VD} = 100$		120		120				dB

† For  $V_{CC\pm} = \pm 5\text{ V}, V_O = \pm 2.3\text{ V},$  at  $V_{CC\pm} = \pm 15\text{ V}, V_O = \pm 10\text{ V}.$

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TL054Y operating characteristics,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TL054Y						UNIT					
		$V_{CC\pm} = \pm 5\text{ V}$			$V_{CC\pm} = \pm 15\text{ V}$								
		MIN	TYP	MAX	MIN	TYP	MAX						
SR+	Positive slew rate at unity gain†	$R_L = 2\text{ k}\Omega$ , See Figure 1		$C_L = 100\text{ pF}$		15.4			17.8			V/ $\mu\text{s}$	
SR-	Negative slew rate at unity gain					13.9			15.9				
$t_r$	Rise time	$V_I(\text{PP}) = \pm 10\text{ mV}$ , $R_L = 2\text{ k}\Omega$ , $C_L = 100\text{ pF}$ , See Figures 1 and 2				55			56			ns	
$t_f$	Fall time					55			57				
	Overshoot factor					24%			19%				
$V_n$	Equivalent input noise voltage‡	$R_S = 20\ \Omega$ , See Figure 3		$f = 10\text{ Hz}$		75			75			nV/ $\sqrt{\text{Hz}}$	
						$f = 1\text{ kHz}$		21			21		
$V_{N(\text{PP})}$	Peak-to-peak equivalent input noise voltage							$f = 10\text{ Hz to } 10\text{ kHz}$		4			4
$I_n$	Equivalent input noise current	$f = 1\text{ kHz}$		0.01			0.01			pA/ $\sqrt{\text{Hz}}$			
THD	Total harmonic distortion§	$R_S = 1\text{ k}\Omega$ , $f = 1\text{ kHz}$		$R_L = 2\text{ k}\Omega$		0.003%			0.003%				
$B_1$	Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $C_L = 25\text{ pF}$		$R_L = 2\text{ k}\Omega$ , See Figure 4		2.7			2.7			MHz	
$\phi_m$	Phase margin at unity gain	$V_I = 10\text{ mV}$ , $C_L = 25\text{ pF}$		$R_L = 2\text{ k}\Omega$ , See Figure 4		61°			64°				

† For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_I(\text{PP}) = \pm 1\text{ V}$ ; for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_I(\text{PP}) = \pm 5\text{ V}$ .

‡ This parameter is tested on a sample basis. For other test requirements, please contact the factory. This statement has no bearing on testing or nontesting of other parameters.

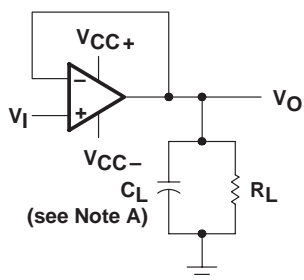
§ For  $V_{CC\pm} = \pm 5\text{ V}$ ,  $V_o(\text{rms}) = 1\text{ V}$ ; for  $V_{CC\pm} = \pm 15\text{ V}$ ,  $V_o(\text{rms}) = 6\text{ V}$ .



# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## PARAMETER MEASUREMENT INFORMATION



NOTE A:  $C_L$  includes fixture capacitance.

Figure 1 . Slew Rate, Rise/Fall Time, and Overshoot Test Circuit

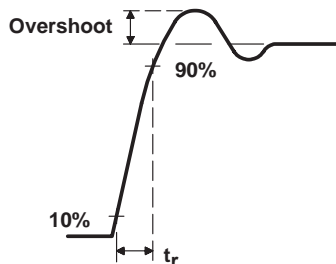


Figure 2 . Rise Time and Overshoot Waveform

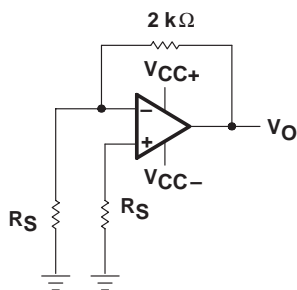
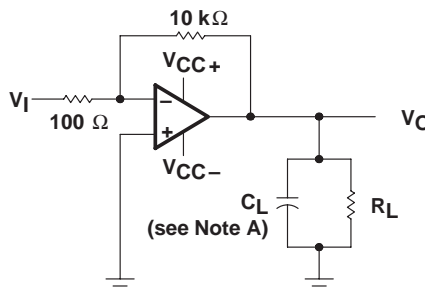


Figure 3 . Noise-Voltage Test Circuit



NOTE A:  $C_L$  includes fixture capacitance.

Figure 4 . Unity-Gain Bandwidth and Phase-Margin Test Circuit

### typical values

Typical values as presented in this data sheet represent the median (50% point) of device parametric performance.

### input bias and offset current

At the picoamp-bias-current level typical of the TL05x and TL05xA, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test socket leakages can easily exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted in the socket, and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.

### noise

Because of the increasing emphasis on low noise levels in many of today's applications, the input noise voltage density is sample tested at  $f = 1$  kHz. Texas Instruments also has additional noise testing capability to meet specific application requirements. Please contact the factory for details.

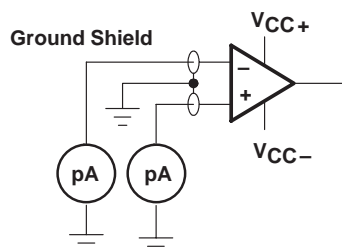


Figure 5. Input-Bias and Offset-Current Test Circuit



**TYPICAL CHARACTERISTICS**

**Table of Graphs**

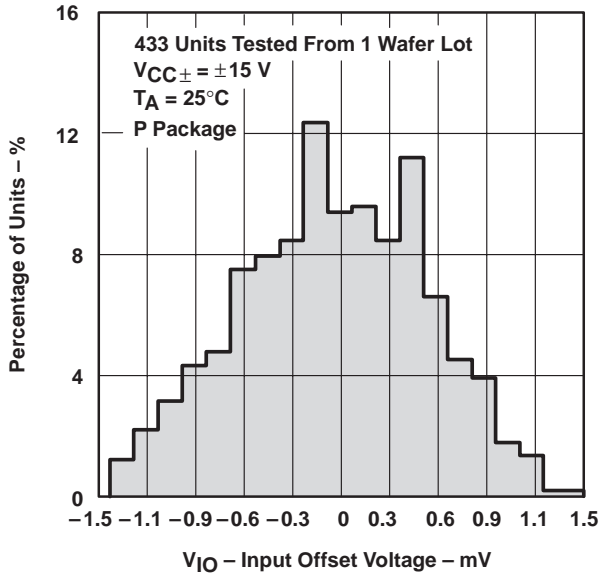
		<b>FIGURE</b>
$V_{IO}$	Input offset voltage	Distribution 6 – 11
$\alpha V_{IO}$	Temperature coefficient of input offset voltage	Distribution 12, 13, 14
$I_{IB}$	Input bias current	vs Common-mode input voltage
		vs Free-air temperature
$I_{IO}$	Input offset current	vs Free-air temperature
$V_{IC}$	Common-mode input voltage range limits	vs Supply voltage
		vs Free-air temperature
$V_O$	Output voltage	vs Differential input voltage
$V_{OM}$	Maximum peak output voltage	vs Supply voltage
		vs Output current
		vs Free-air temperature
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency
$A_{VD}$	Large-signal differential voltage amplification	vs Load resistance
		vs Frequency
		vs Free-air temperature
CMRR	Common-mode rejection ratio	vs Frequency
		vs Free-air temperature
$z_o$	Output impedance	vs Frequency
$k_{SVR}$	Supply-voltage rejection ratio	vs Free-air temperature
$I_{OS}$	Short-circuit output current	vs Supply voltage
		vs Time
		vs Free-air temperature
$I_{CC}$	Supply current	vs Supply voltage
		vs Free-air temperature
SR	Slew rate	vs Load resistance
		vs Free-air temperature
	Overshoot factor	vs Load capacitance
$V_n$	Equivalent input noise voltage	vs Frequency
THD	Total harmonic distortion	vs Frequency
$B_1$	Unity-gain bandwidth	vs Supply voltage
		vs Free-air temperature
$\phi_m$	Phase margin	vs Supply voltage
		vs Load capacitance
		vs Free-air temperature
	Phase shift	vs Frequency
	Voltage-follower small-signal pulse response	vs Time
	Voltage-follower large-signal pulse response	vs Time

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

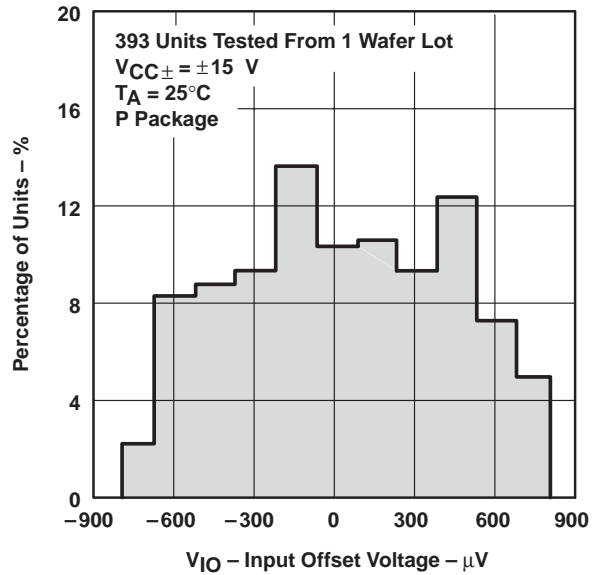
**TYPICAL CHARACTERISTICS**

**DISTRIBUTION OF TL051**  
**INPUT OFFSET VOLTAGE**



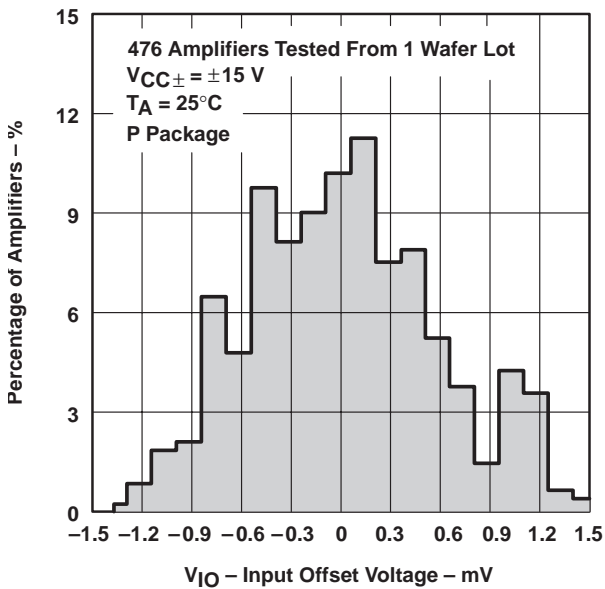
**Figure 6**

**DISTRIBUTION OF TL051A**  
**INPUT OFFSET VOLTAGE**



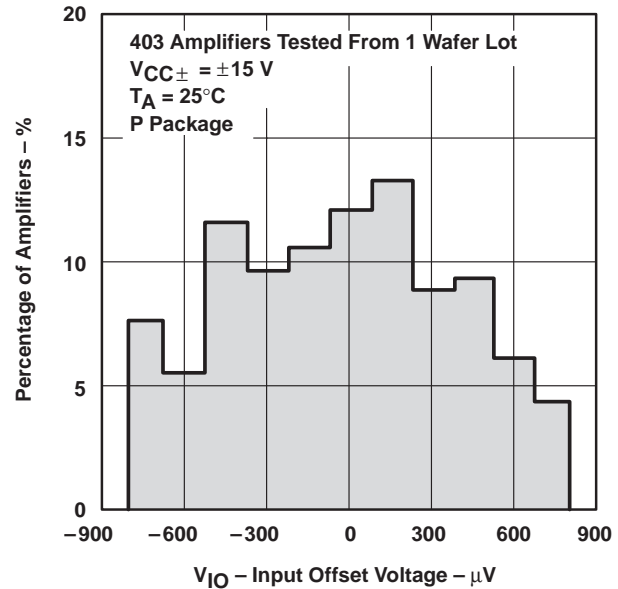
**Figure 7**

**DISTRIBUTION OF TL052**  
**INPUT OFFSET VOLTAGE**



**Figure 8**

**DISTRIBUTION OF TL052A**  
**INPUT OFFSET VOLTAGE**



**Figure 9**

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TL054  
 INPUT OFFSET VOLTAGE

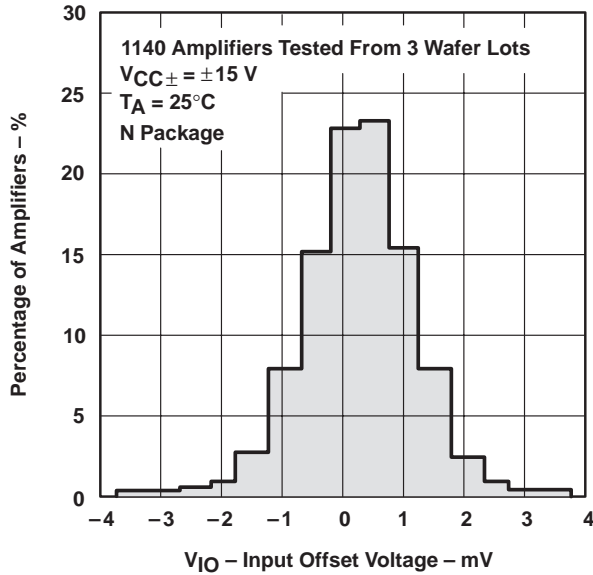


Figure 10

DISTRIBUTION OF TL054A  
 INPUT OFFSET VOLTAGE

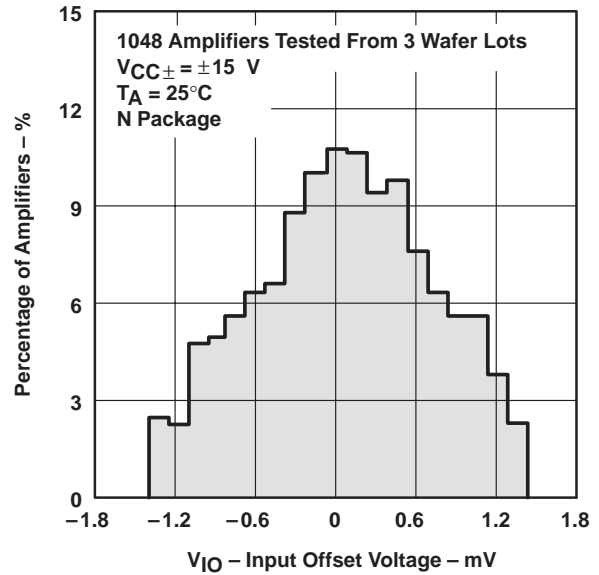


Figure 11

DISTRIBUTION OF TL051  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

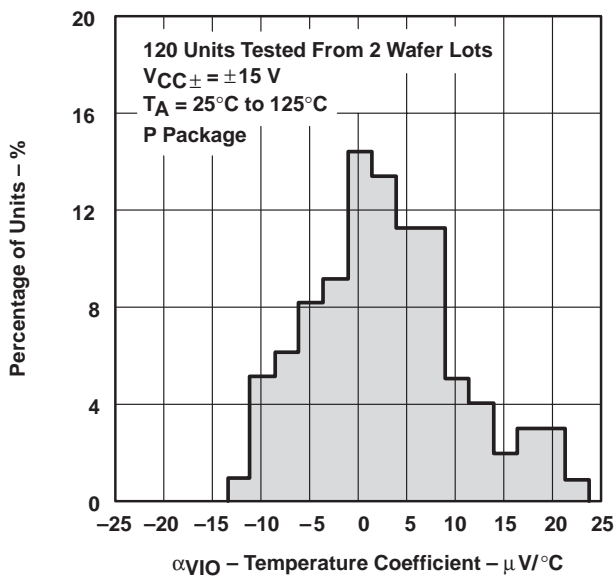


Figure 12

DISTRIBUTION OF TL052  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

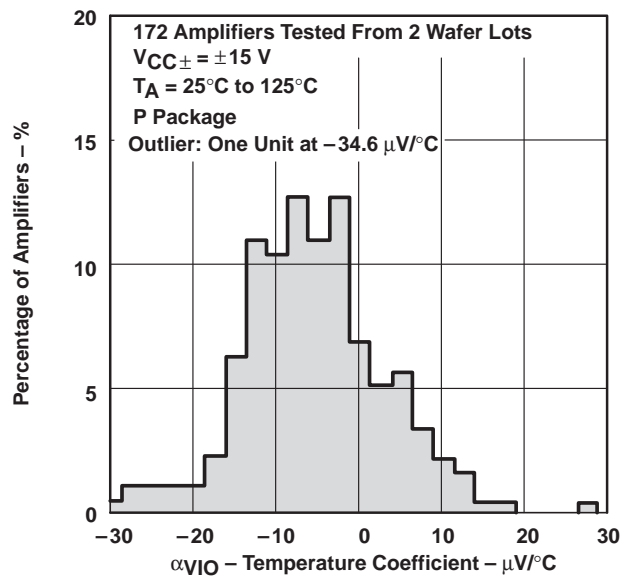


Figure 13

TL05x, TL05xA, TL05xY  
 ENHANCED-JFET LOW-OFFSET  
 OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TL054  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

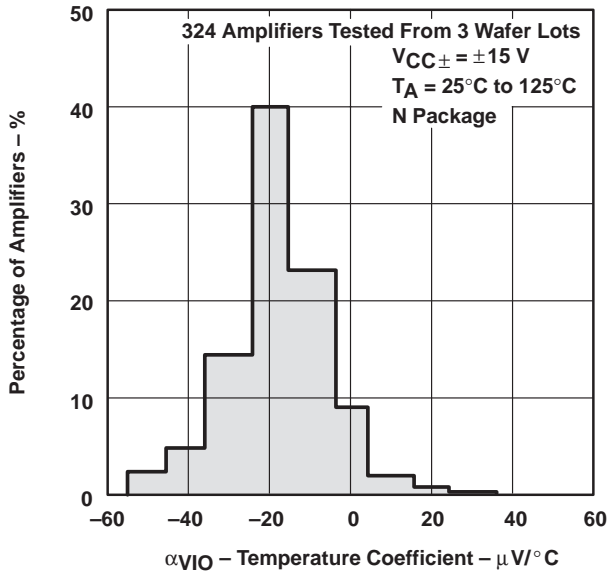


Figure 14

INPUT BIAS CURRENT  
 vs  
 COMMON-MODE INPUT VOLTAGE

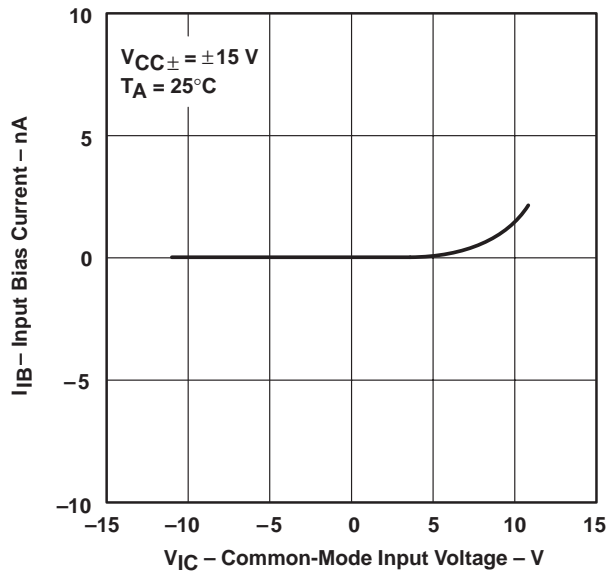


Figure 15

INPUT BIAS CURRENT AND  
 INPUT OFFSET CURRENT†  
 vs  
 FREE-AIR TEMPERATURE

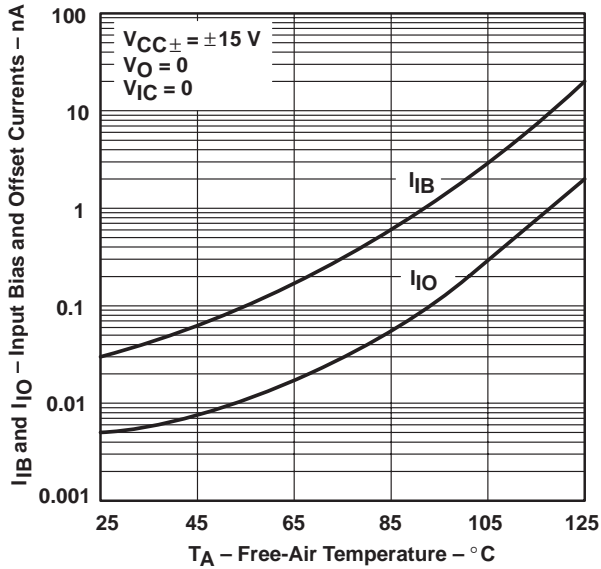


Figure 16

COMMON-MODE  
 INPUT VOLTAGE RANGE LIMITS  
 vs  
 SUPPLY VOLTAGE

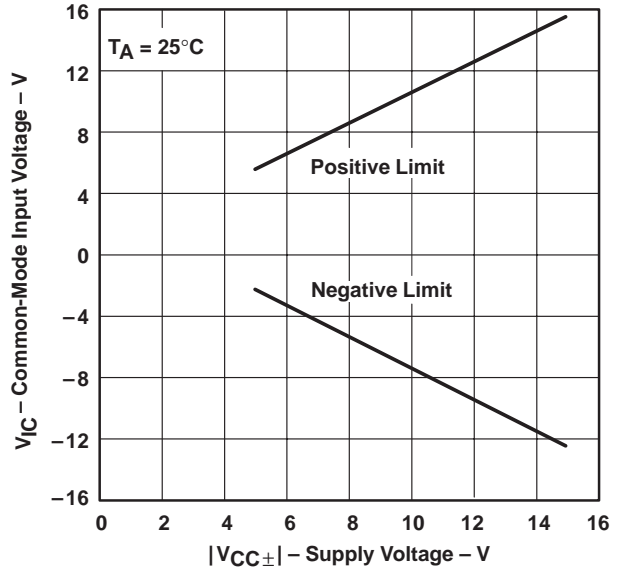


Figure 17

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

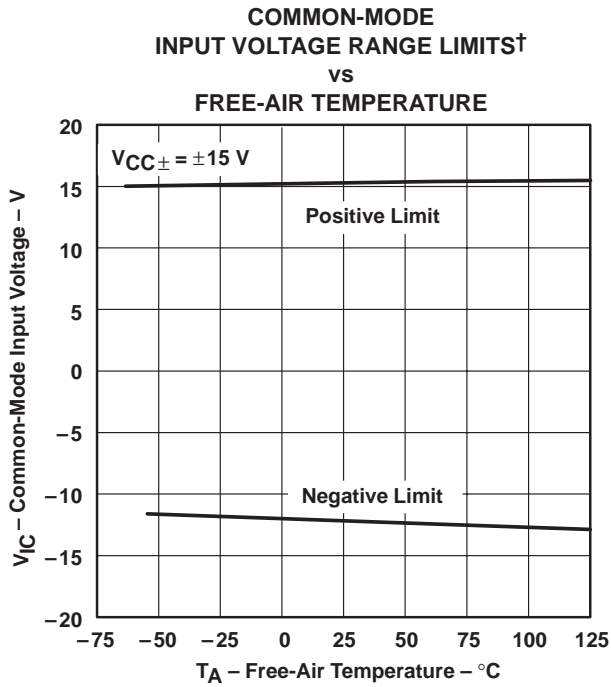


Figure 18

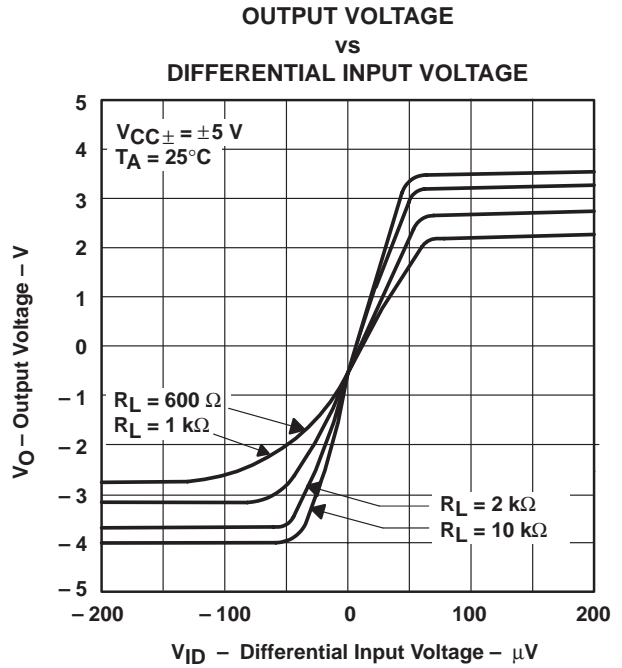


Figure 19

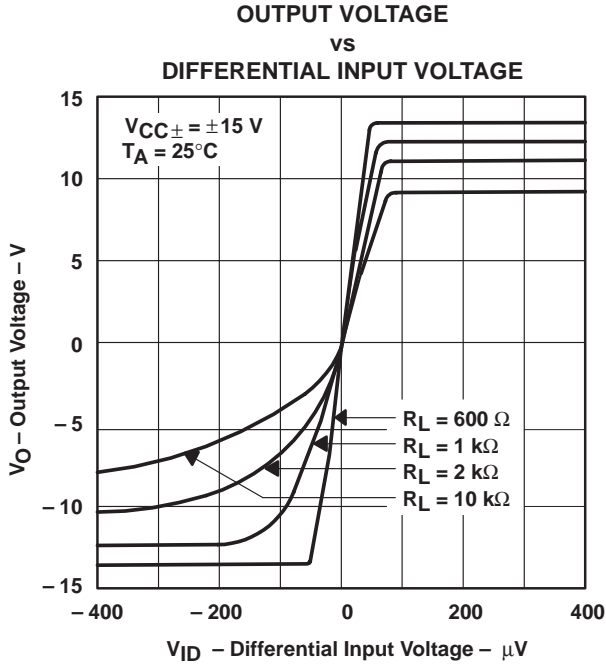


Figure 20

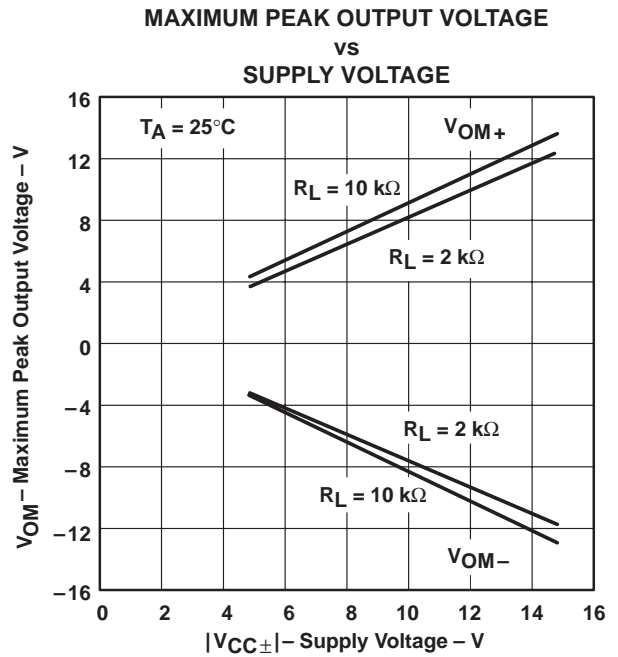


Figure 21

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE†  
 vs  
 FREQUENCY

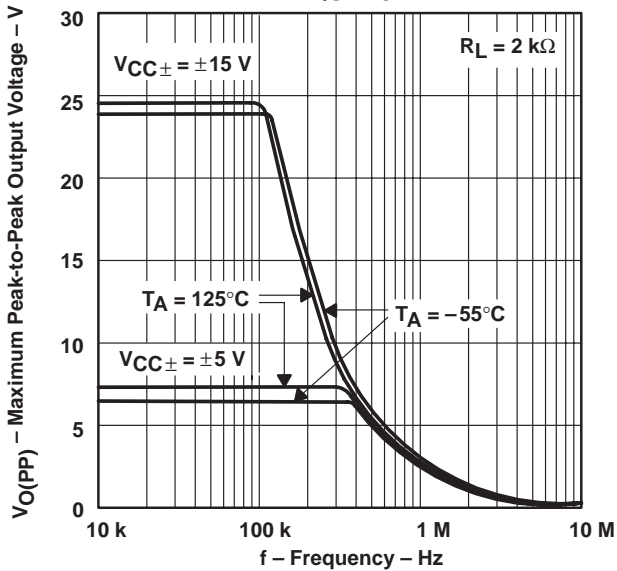


Figure 22

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE  
 vs  
 FREQUENCY

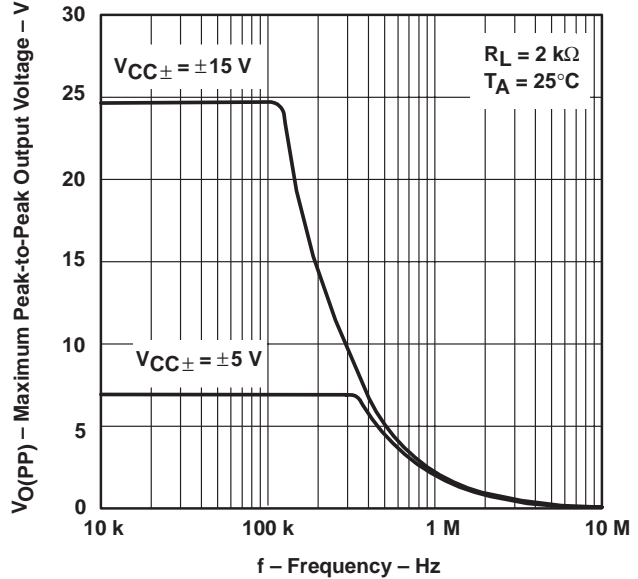


Figure 23

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE  
 vs  
 FREQUENCY

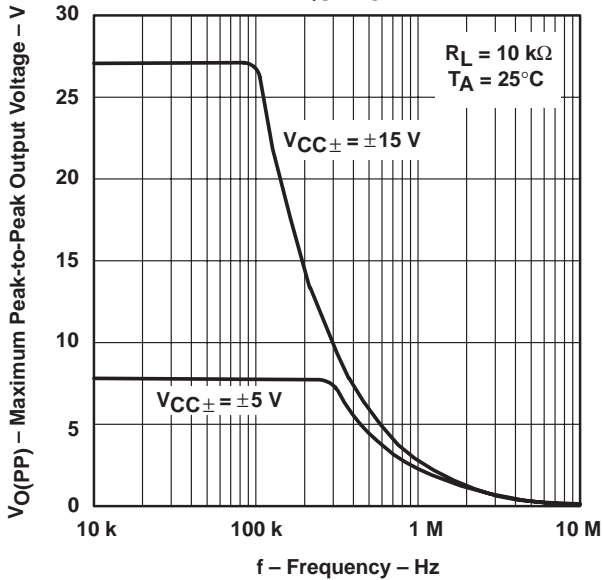


Figure 24

MAXIMUM PEAK OUTPUT VOLTAGE  
 vs  
 OUTPUT CURRENT

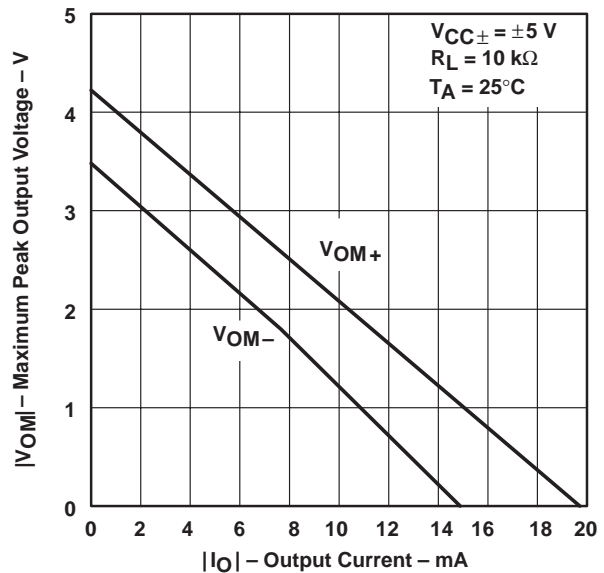


Figure 25

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

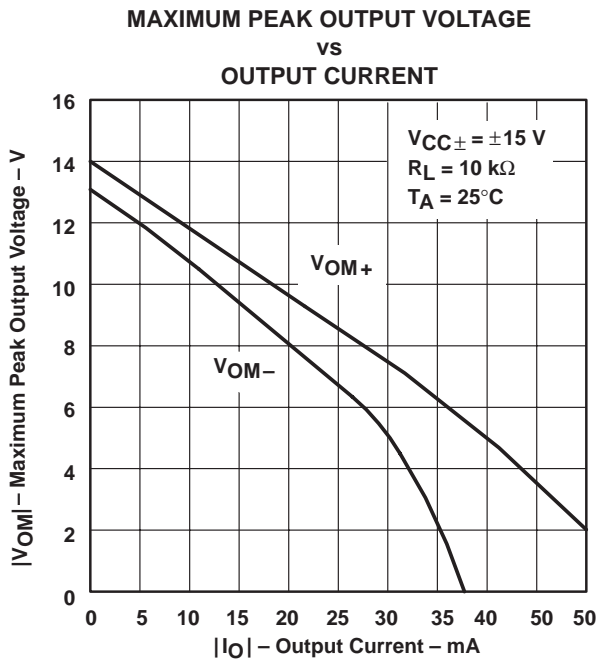


Figure 26

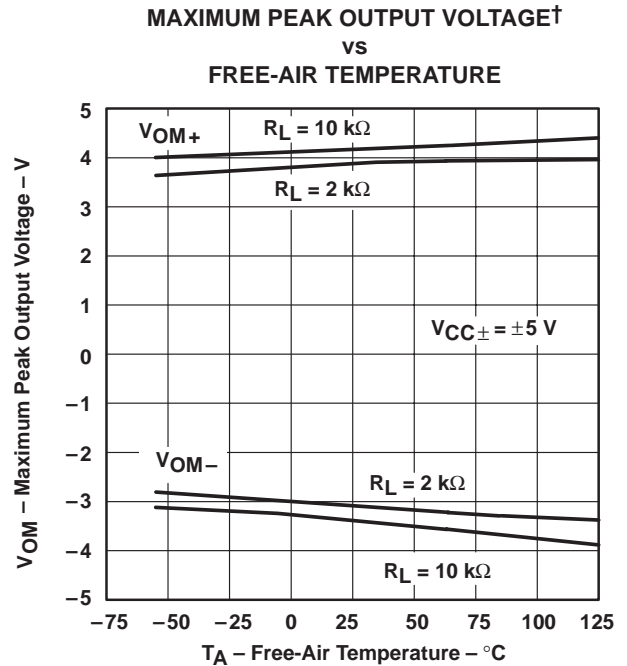


Figure 27

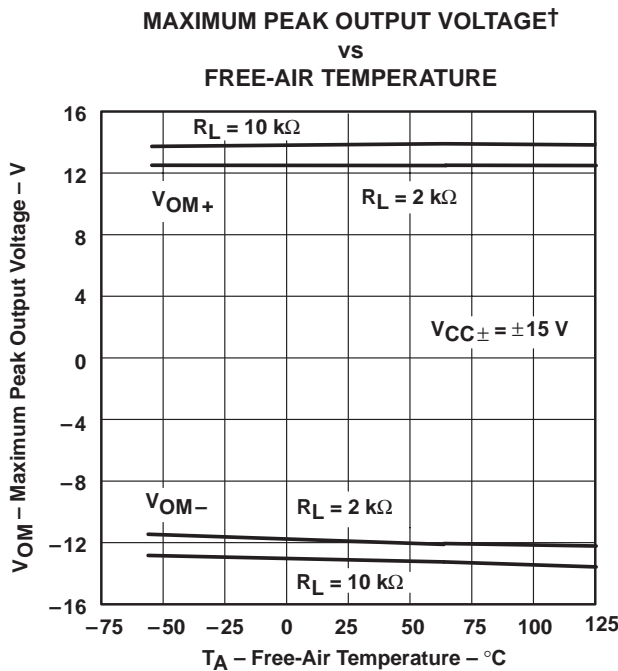


Figure 28

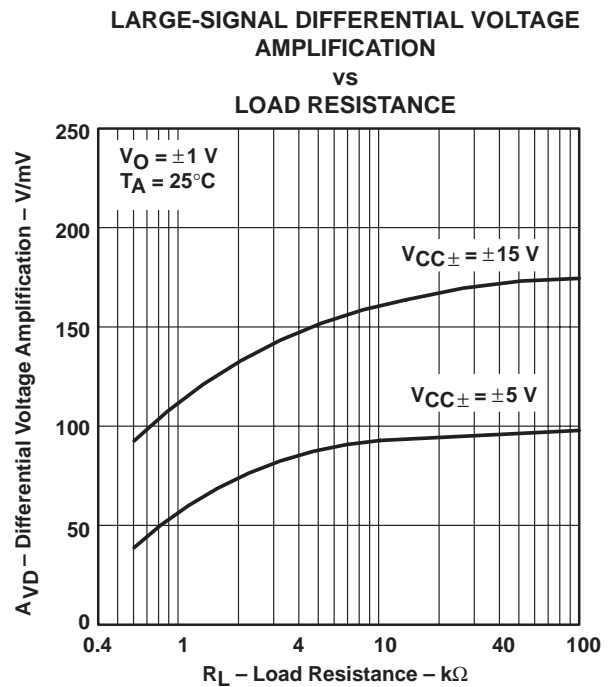


Figure 29

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE  
 AMPLIFICATION AND PHASE SHIFT  
 vs  
 FREQUENCY

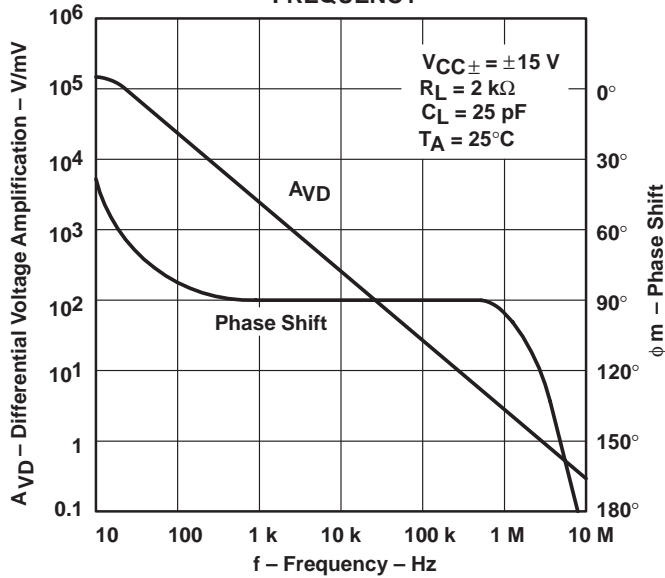


Figure 30

TL051 AND TL052  
 LARGE-SIGNAL DIFFERENTIAL  
 VOLTAGE AMPLIFICATION†  
 vs  
 FREE-AIR TEMPERATURE

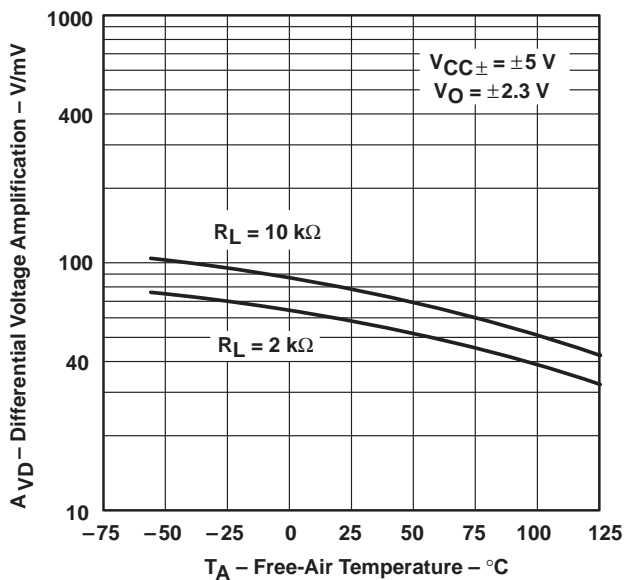


Figure 31

TL054  
 LARGE-SIGNAL DIFFERENTIAL  
 VOLTAGE AMPLIFICATION†  
 vs  
 FREE-AIR TEMPERATURE

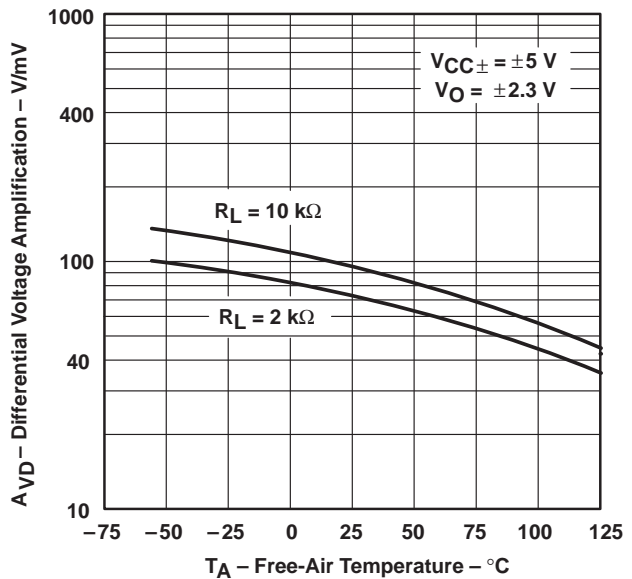


Figure 32

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE  
 AMPLIFICATION†  
 vs  
 FREE-AIR TEMPERATURE

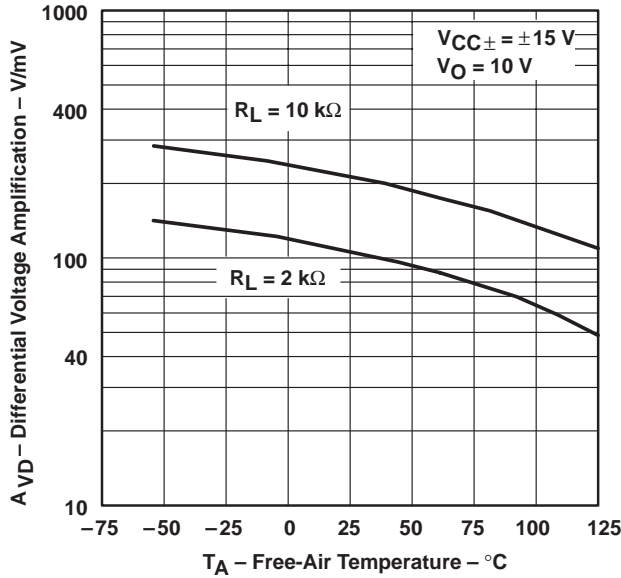


Figure 33

COMMON-MODE REJECTION RATIO  
 vs  
 FREQUENCY

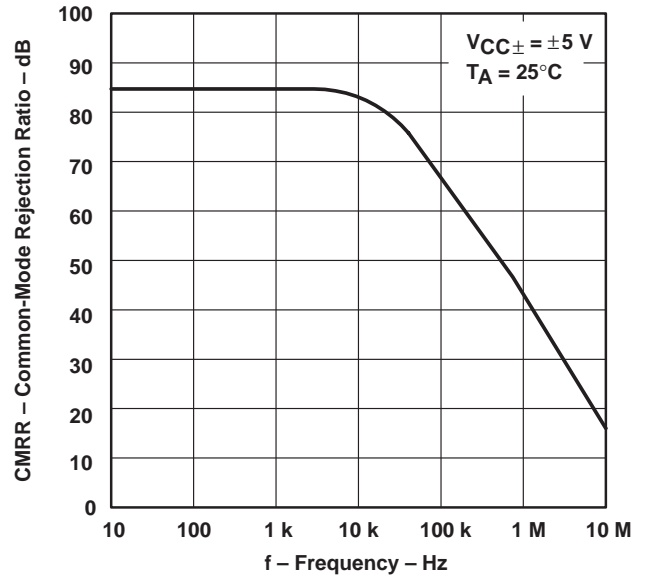


Figure 34

COMMON-MODE REJECTION RATIO  
 vs  
 FREQUENCY

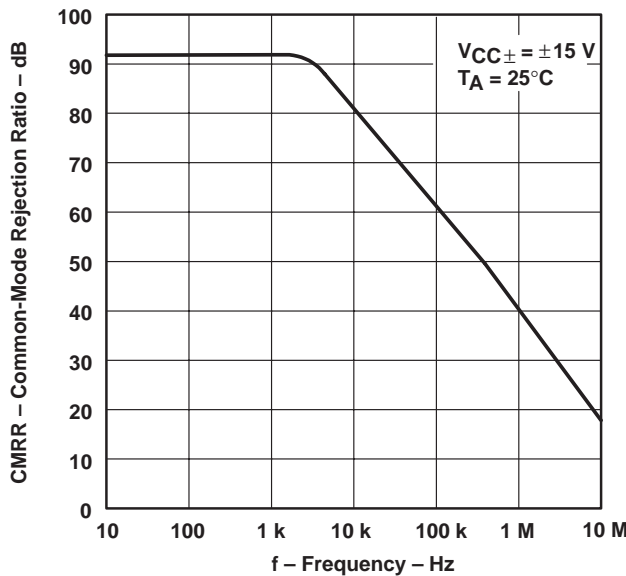


Figure 35

COMMON-MODE REJECTION RATIO†  
 vs  
 FREE-AIR TEMPERATURE

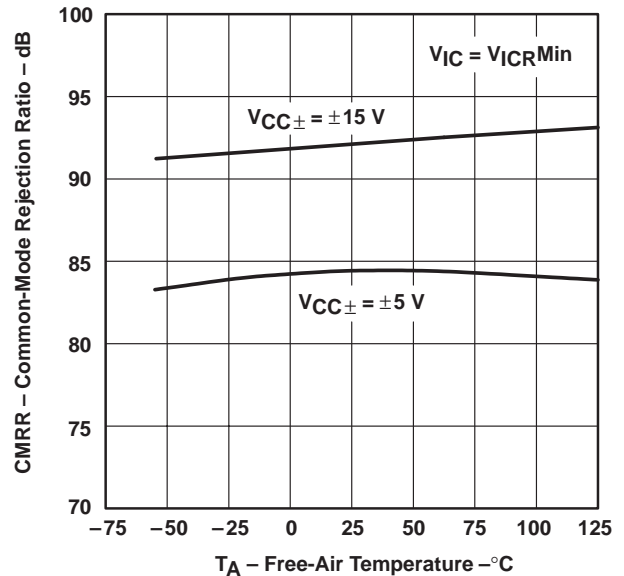


Figure 36

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TL05x, TL05xA, TL05xY  
 ENHANCED-JFET LOW-OFFSET  
 OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

TYPICAL CHARACTERISTICS

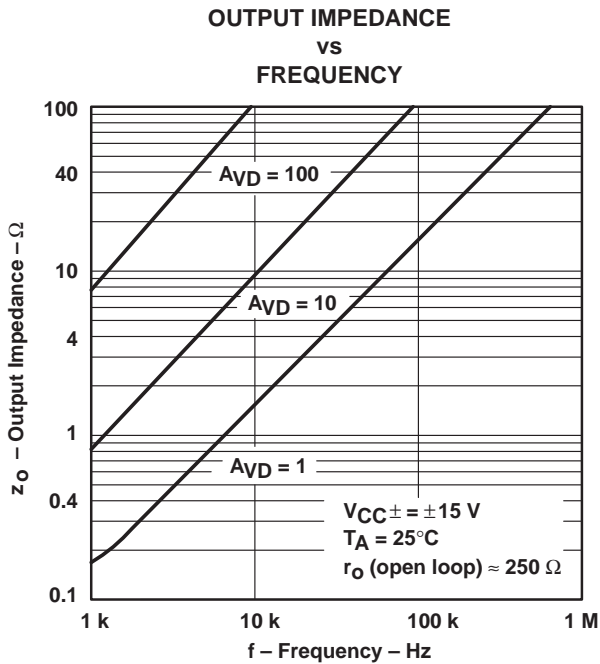


Figure 37

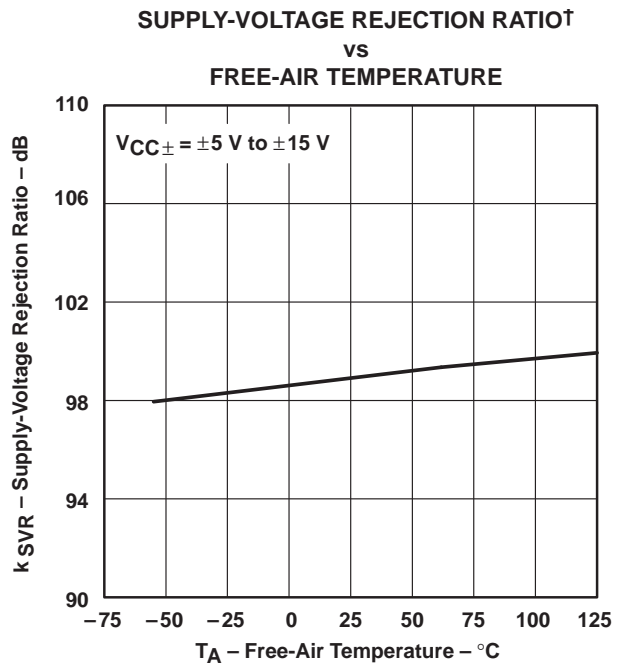


Figure 38

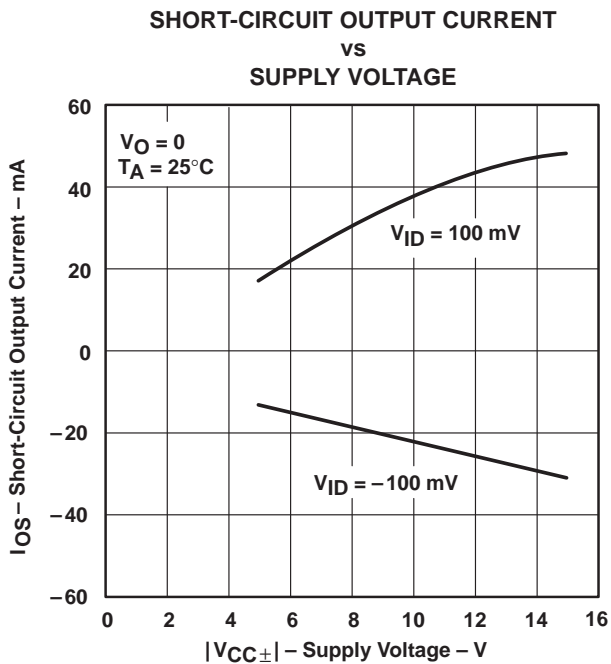


Figure 39

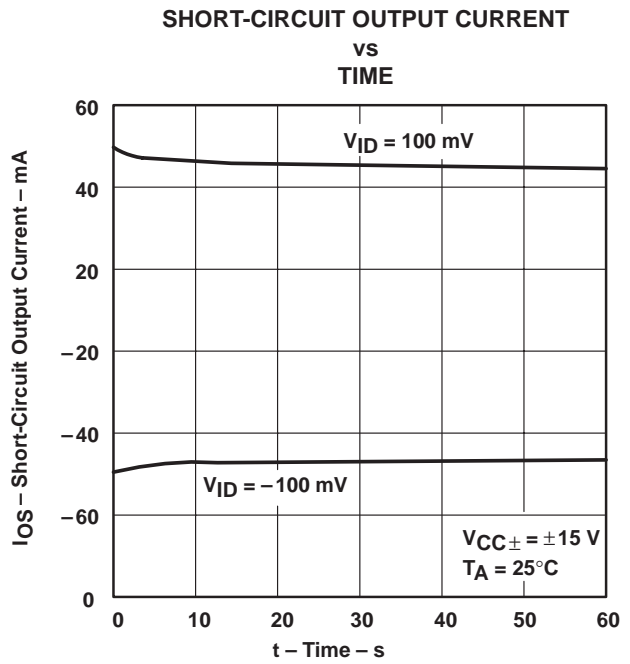


Figure 40

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS

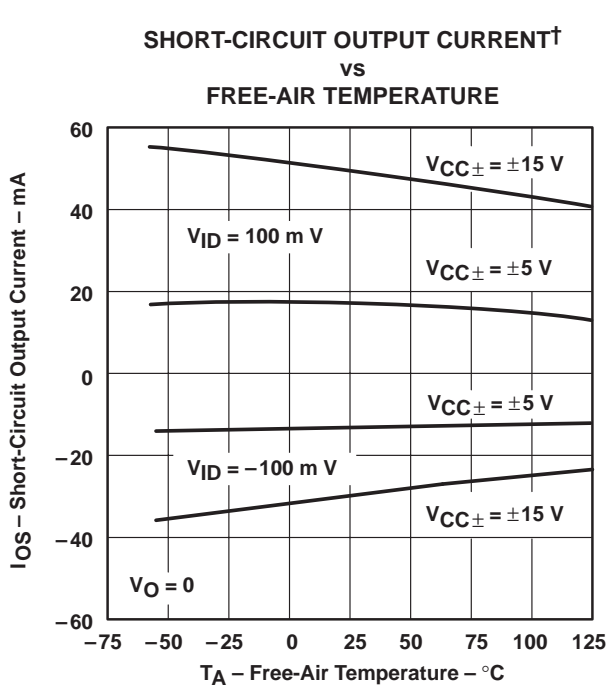


Figure 41

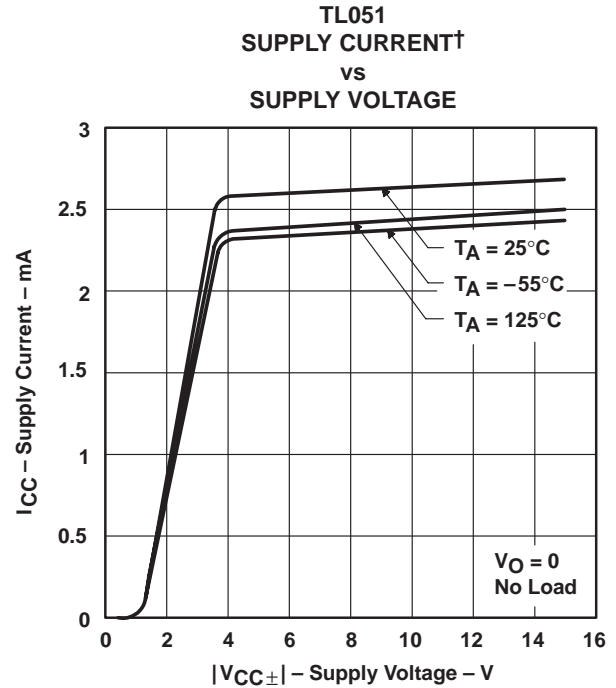


Figure 42

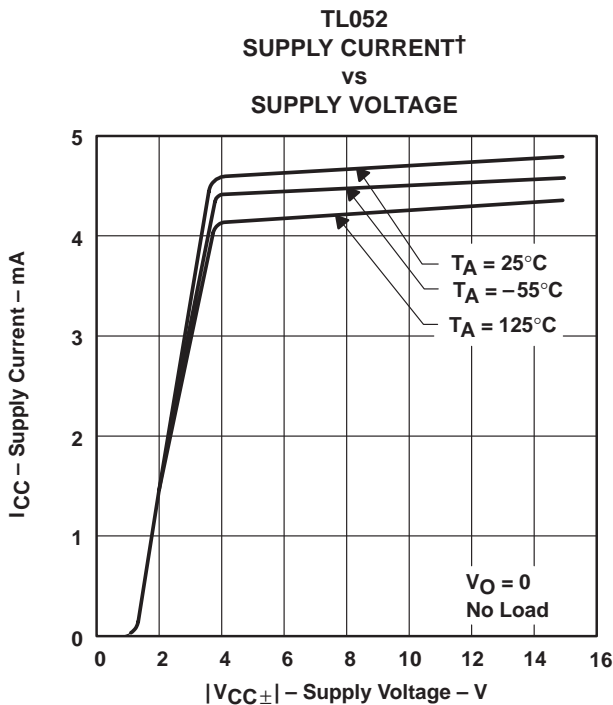


Figure 43

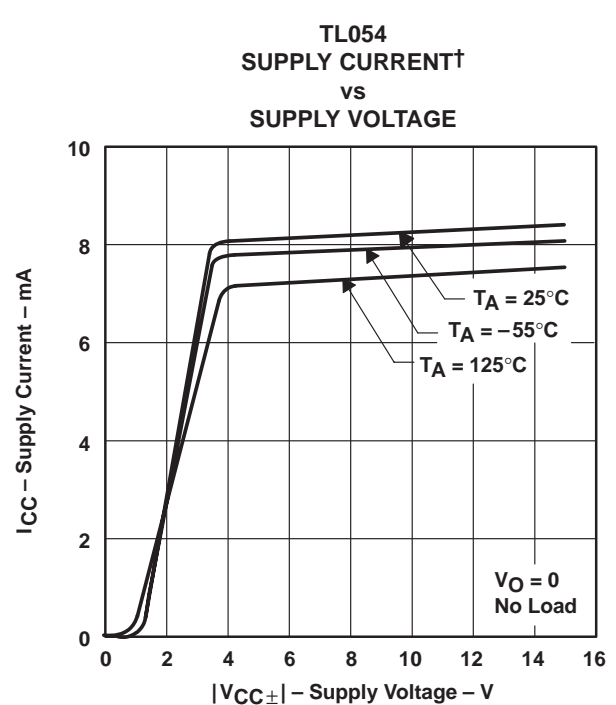


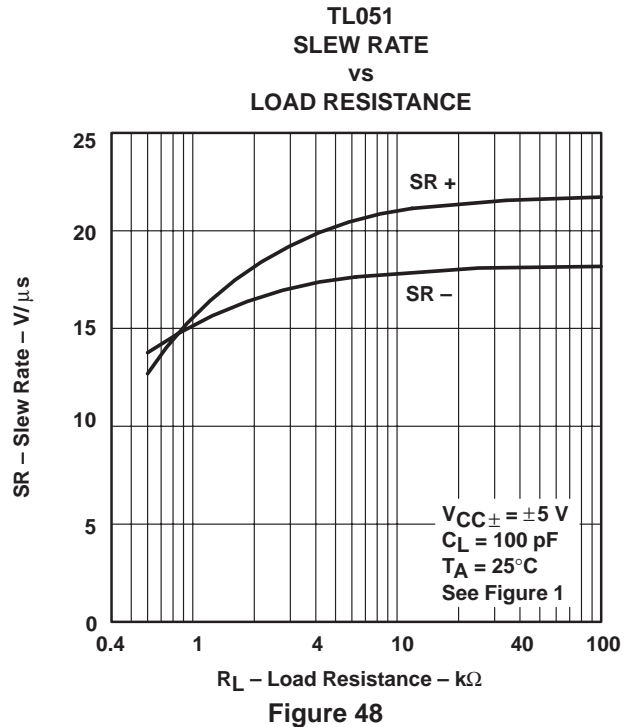
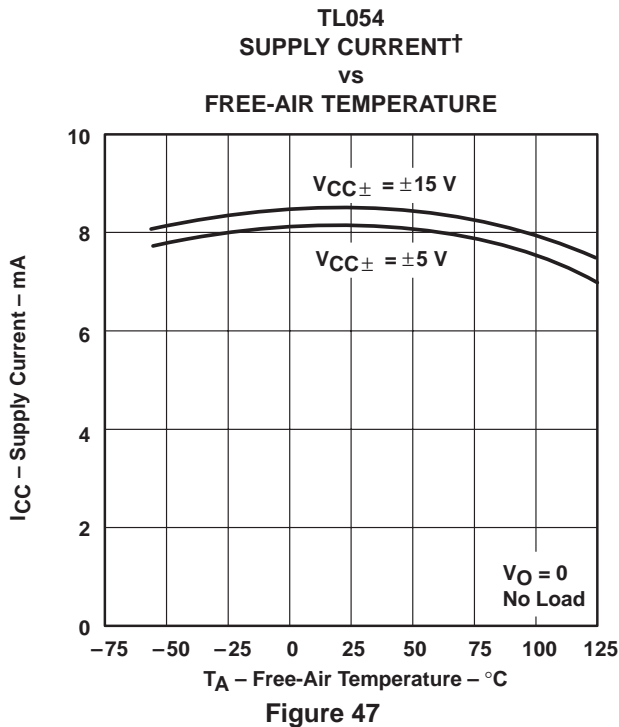
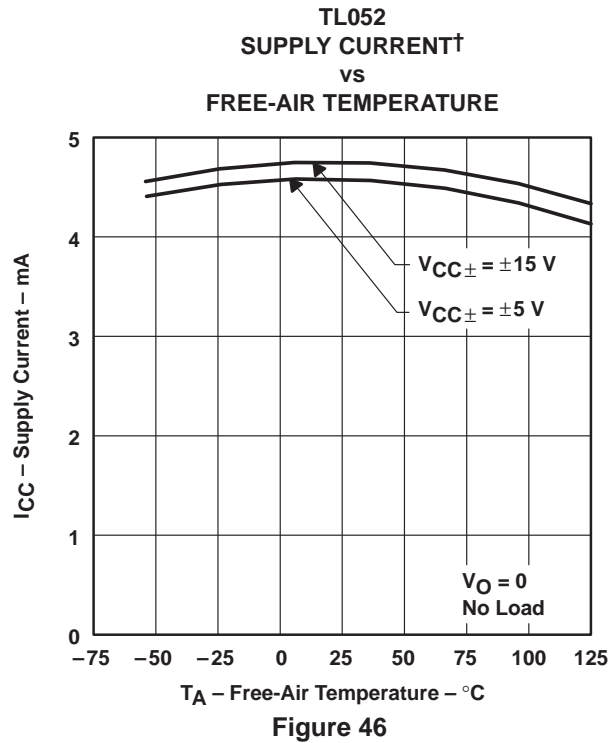
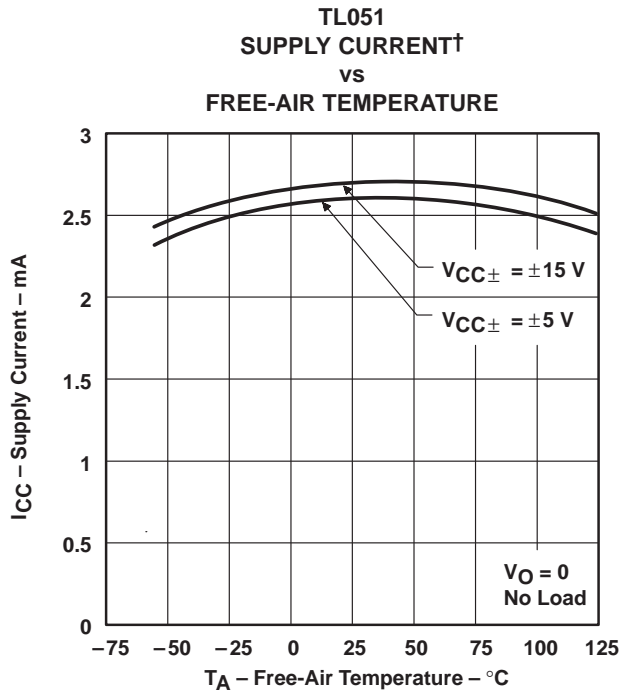
Figure 44

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TYPICAL CHARACTERISTICS**



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS

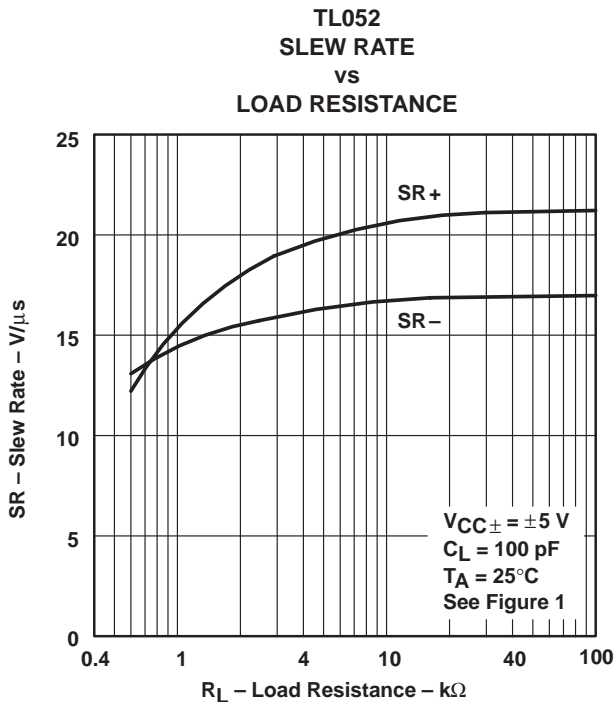


Figure 49

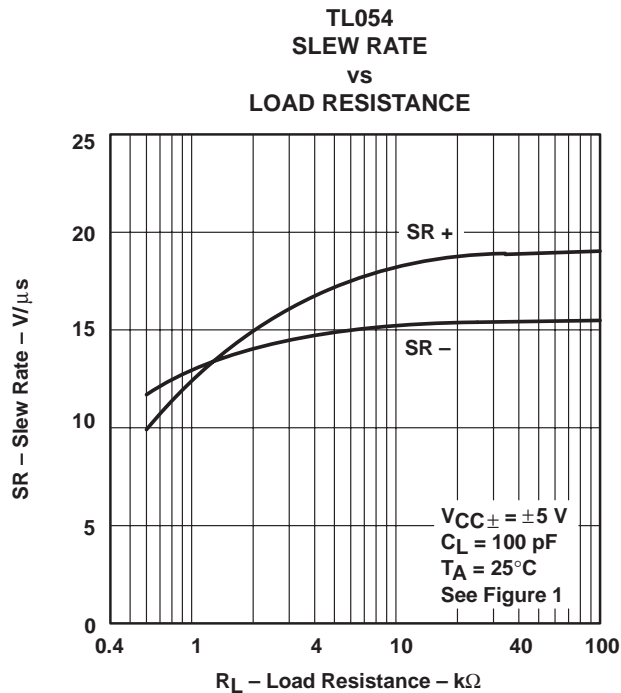


Figure 50

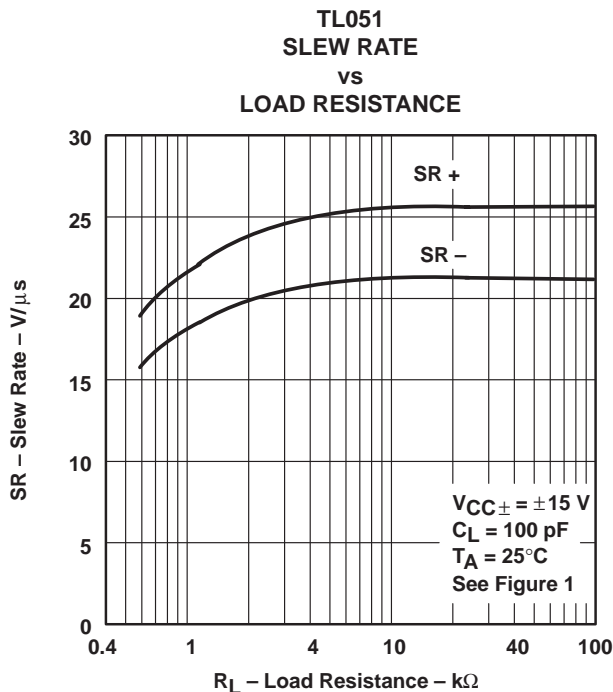


Figure 51

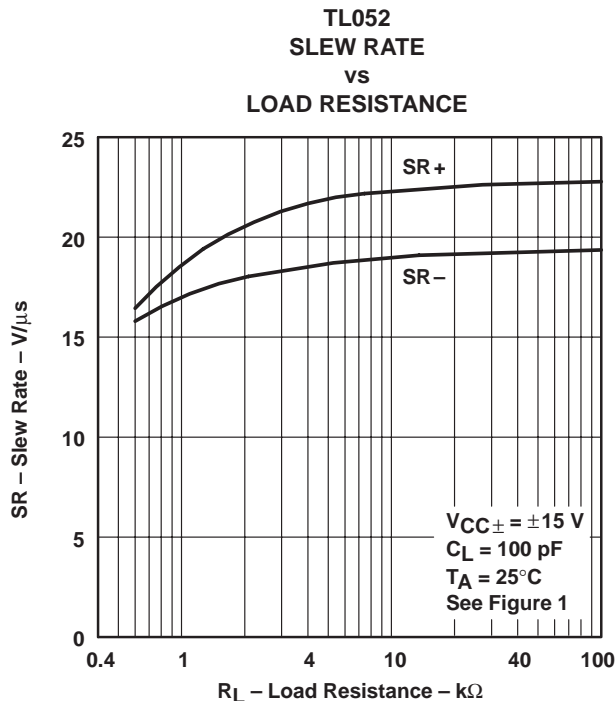
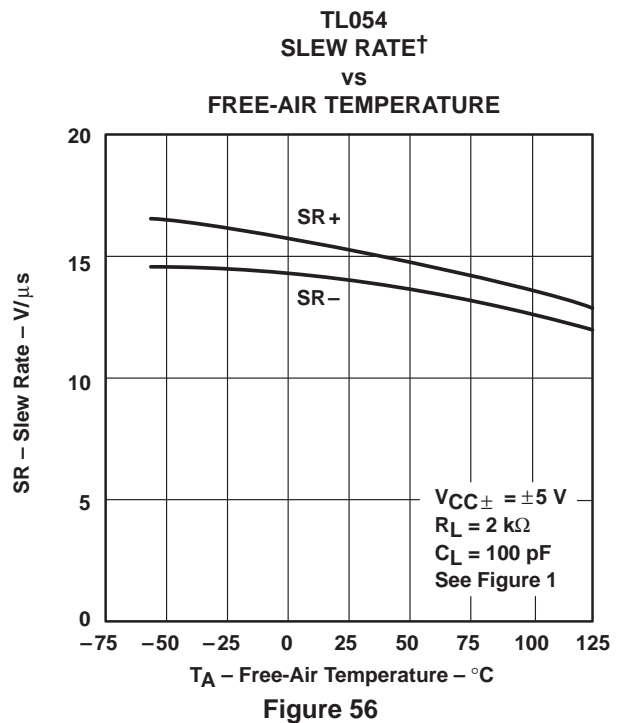
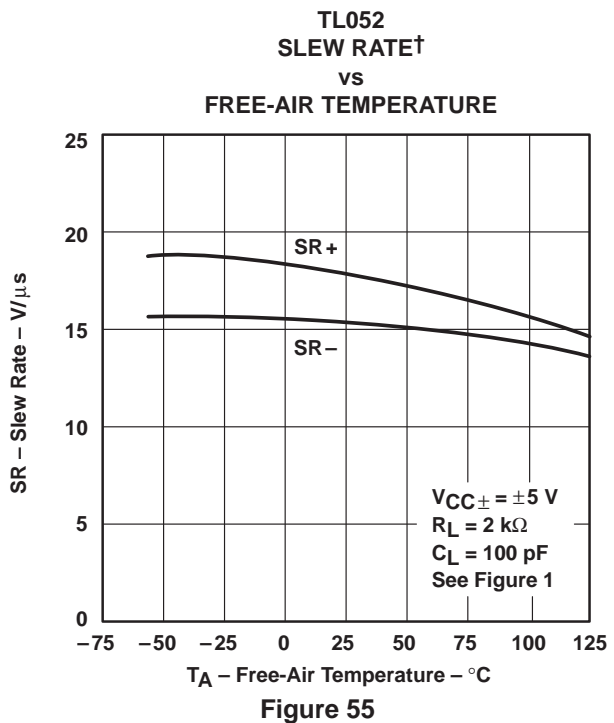
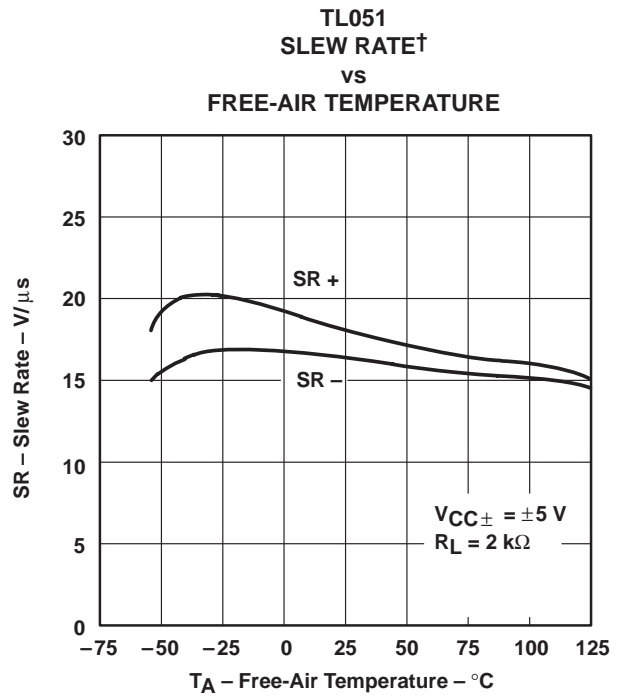
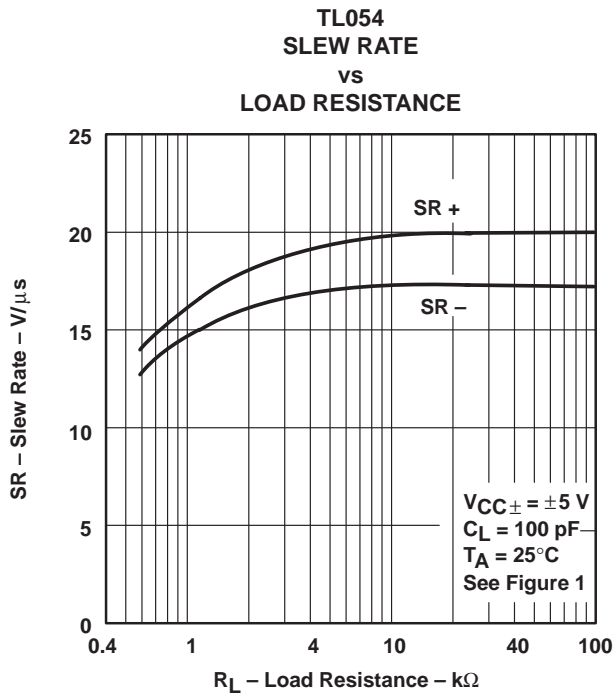


Figure 52

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

**TYPICAL CHARACTERISTICS**



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TYPICAL CHARACTERISTICS

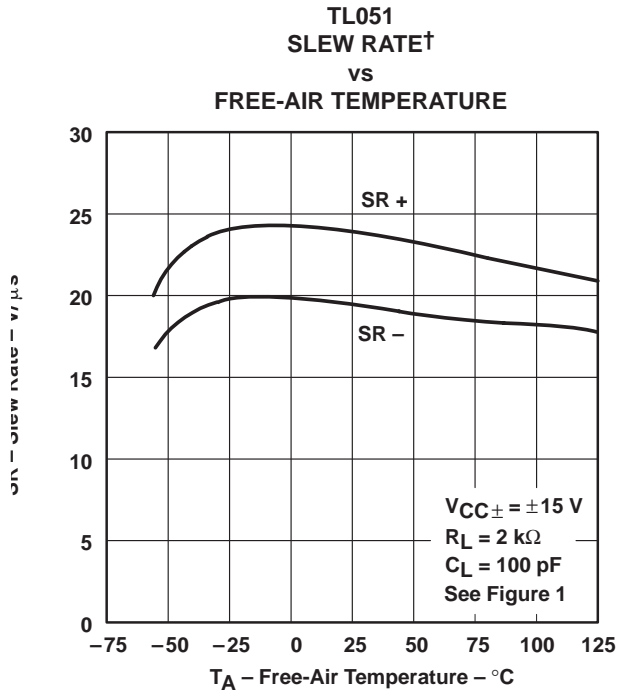


Figure 57

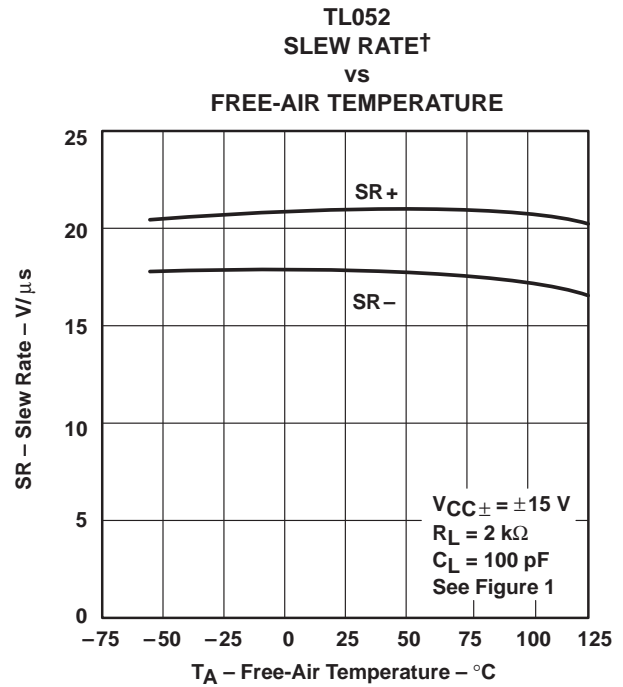


Figure 58

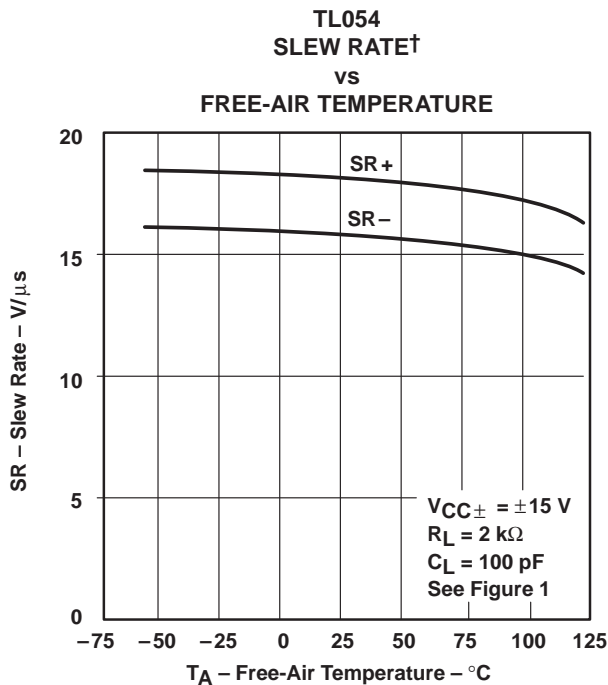


Figure 59

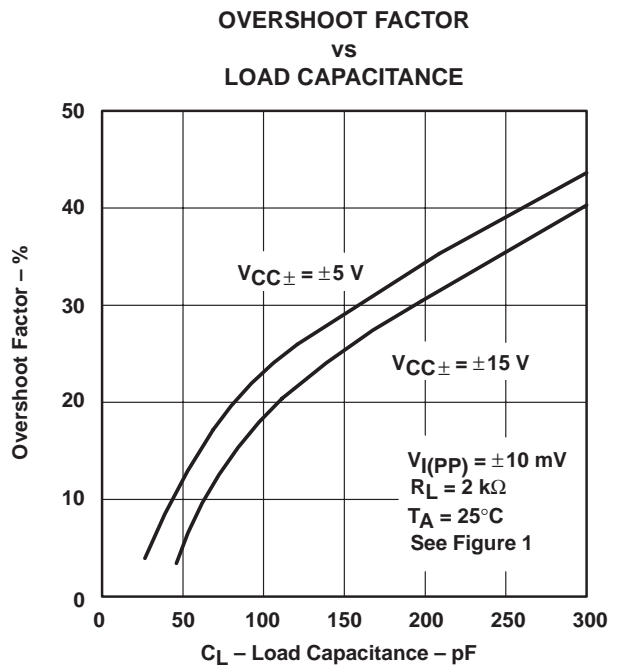


Figure 60

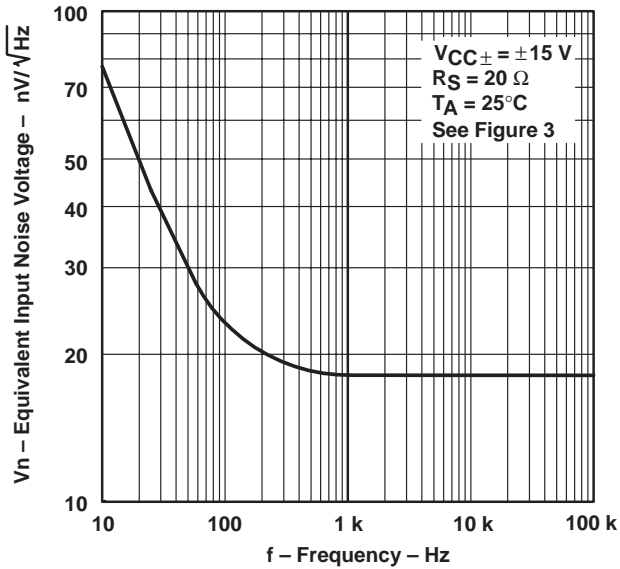
† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

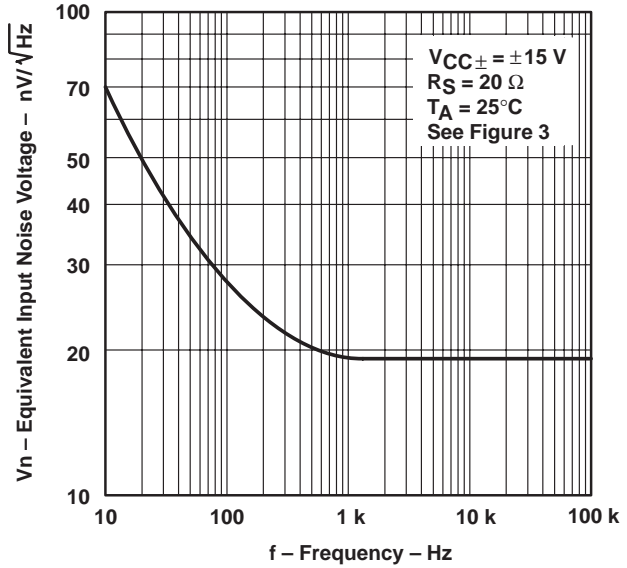
**TYPICAL CHARACTERISTICS**

**TL051**  
**EQUIVALENT INPUT NOISE VOLTAGE**  
**vs**  
**FREQUENCY**



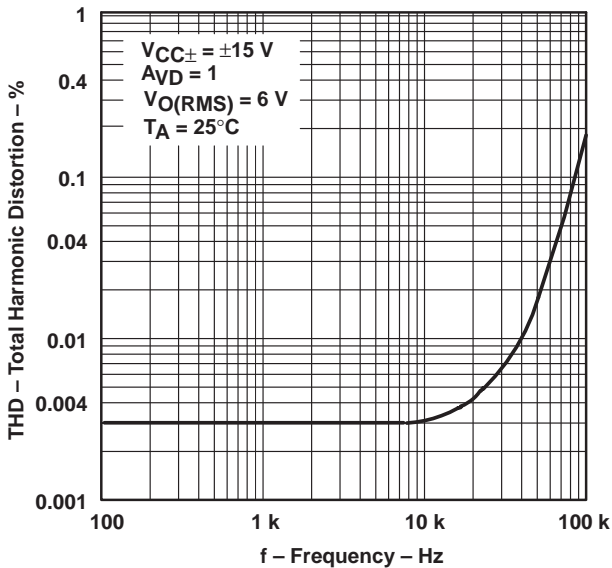
**Figure 61**

**TL052 AND TL054**  
**EQUIVALENT INPUT NOISE VOLTAGE**  
**vs**  
**FREQUENCY**



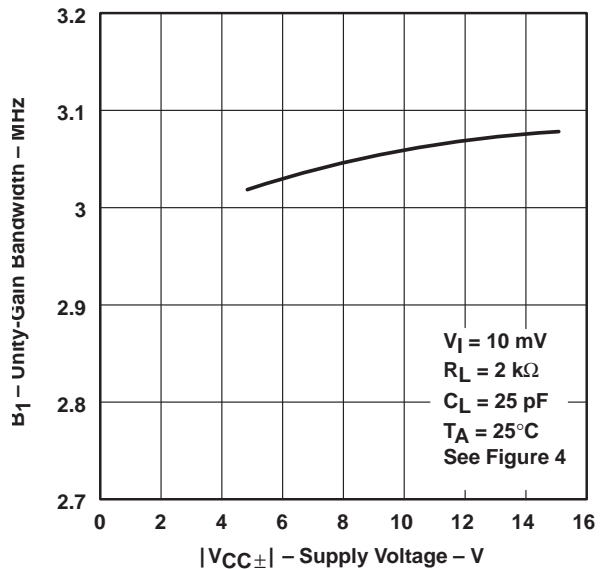
**Figure 62**

**TOTAL HARMONIC DISTORTION**  
**vs**  
**FREQUENCY**



**Figure 63**

**TL051**  
**UNITY-GAIN BANDWIDTH**  
**vs**  
**SUPPLY VOLTAGE**

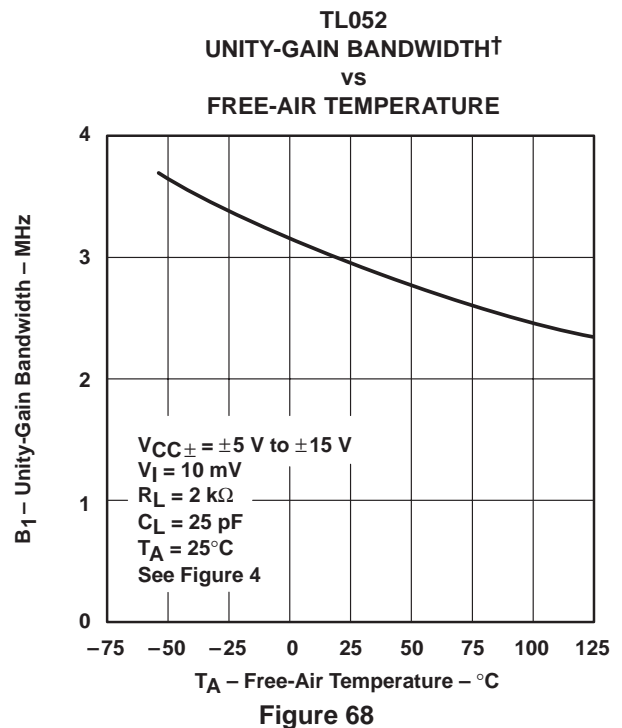
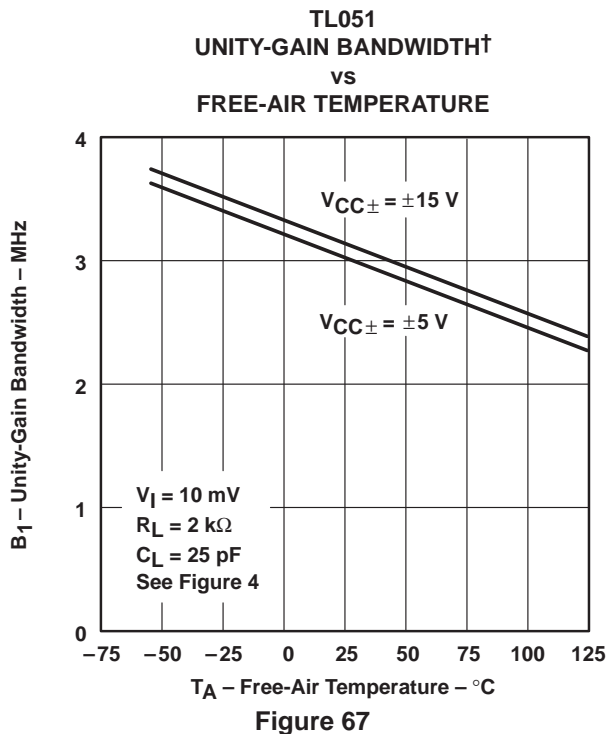
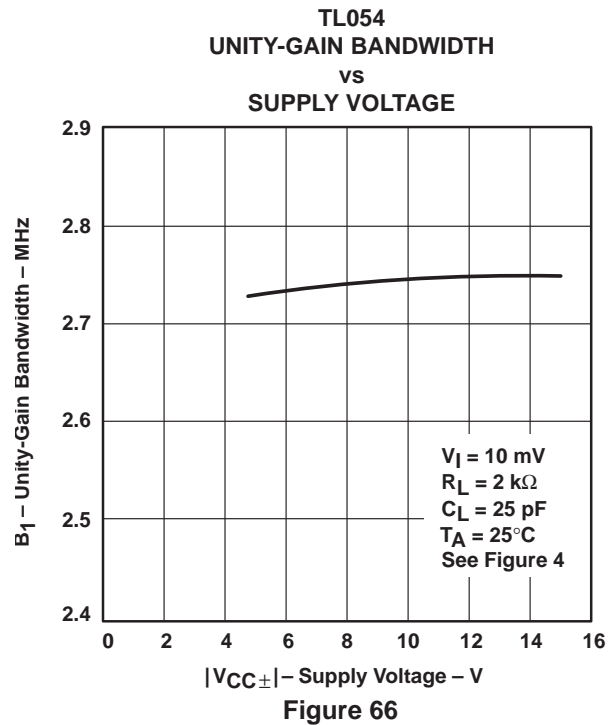
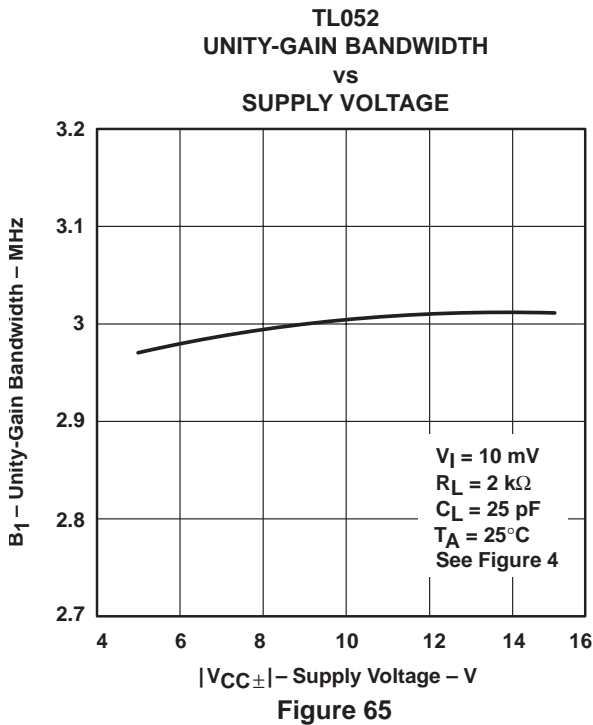


**Figure 64**





TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

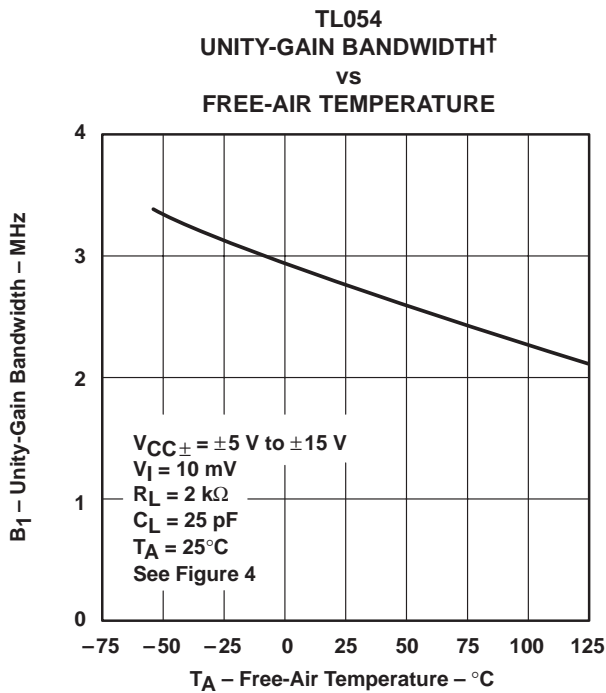


Figure 69

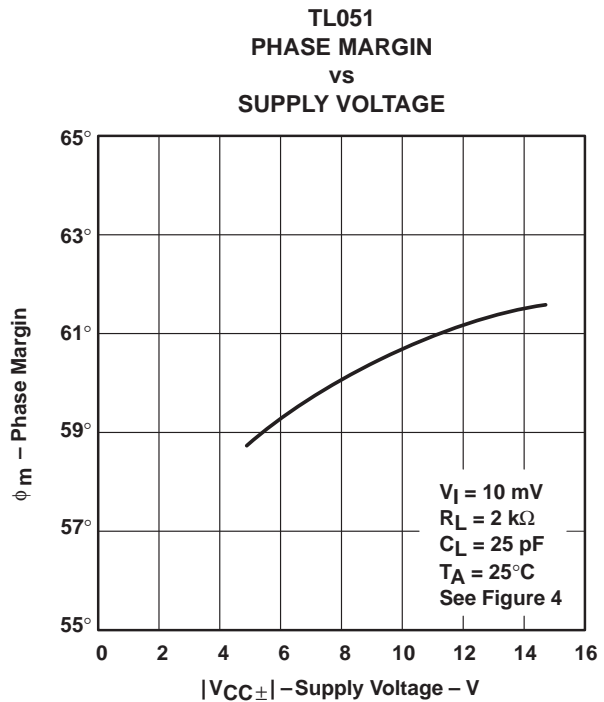


Figure 70

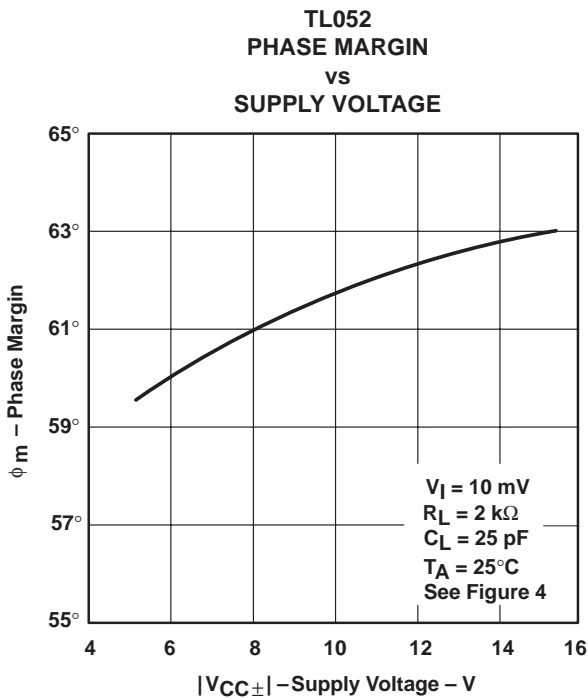


Figure 71

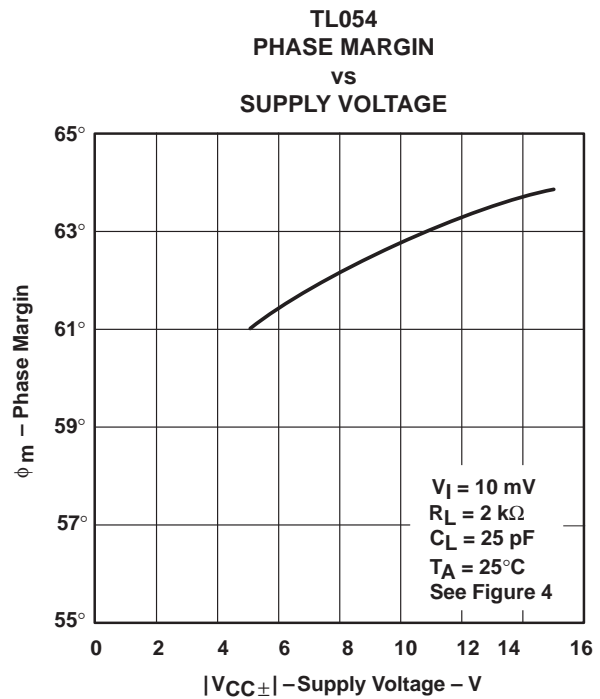
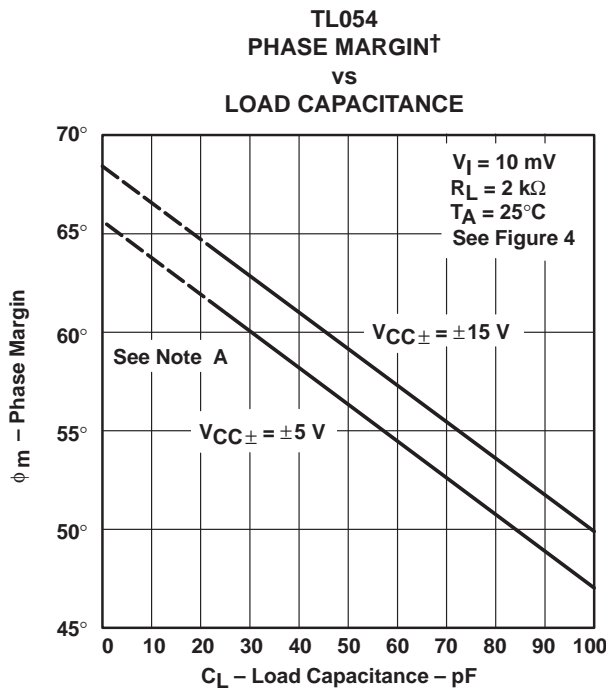
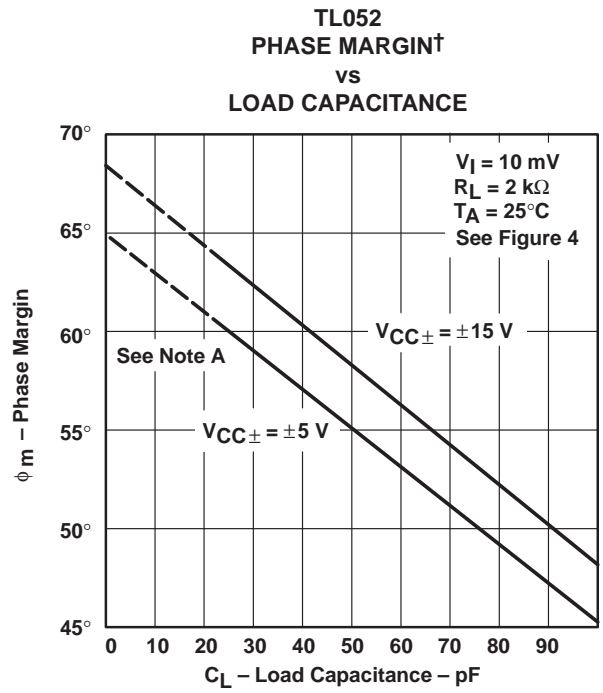
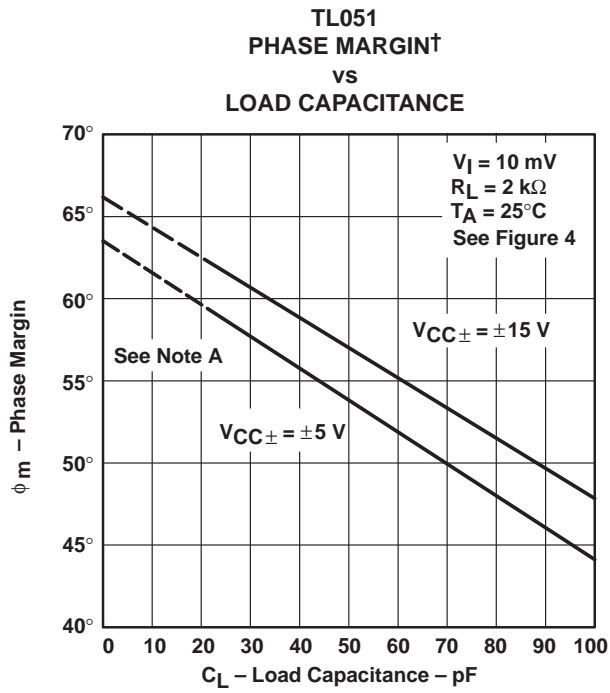


Figure 72

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

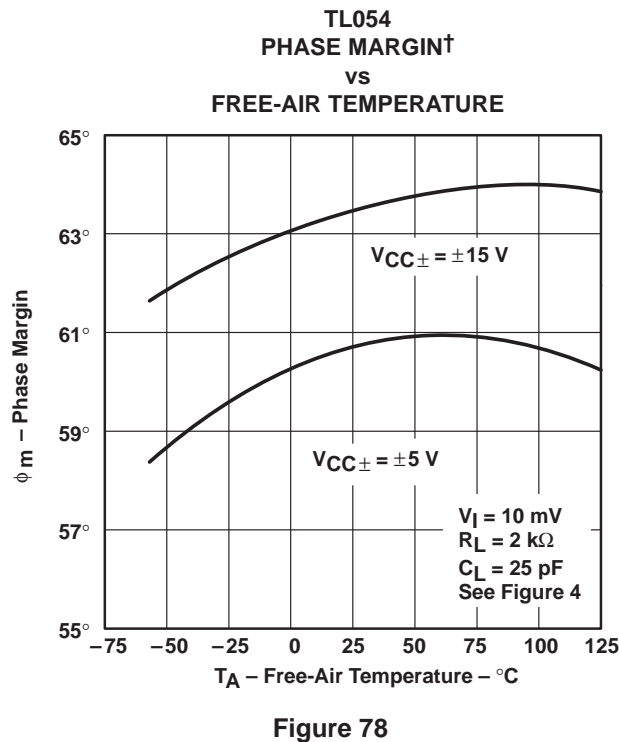
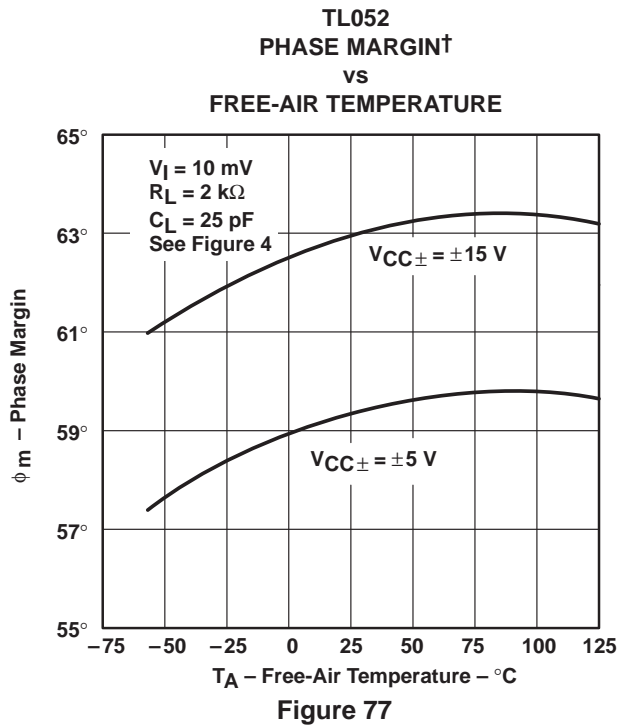
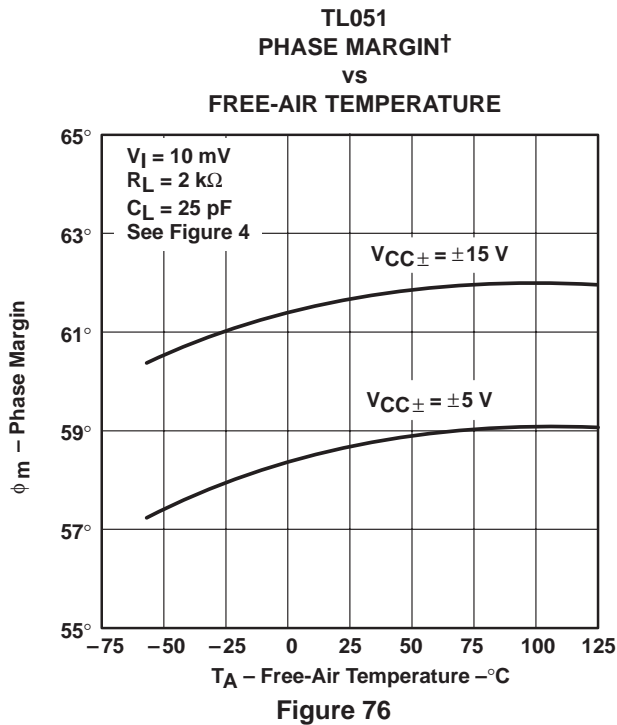


† Values of phase margin below a load capacitance of 25 pF were estimated.

TL05x, TL05xA, TL05xY  
 ENHANCED-JFET LOW-OFFSET  
 OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

VOLTAGE-FOLLOWER  
 SMALL-SIGNAL  
 PULSE RESPONSE

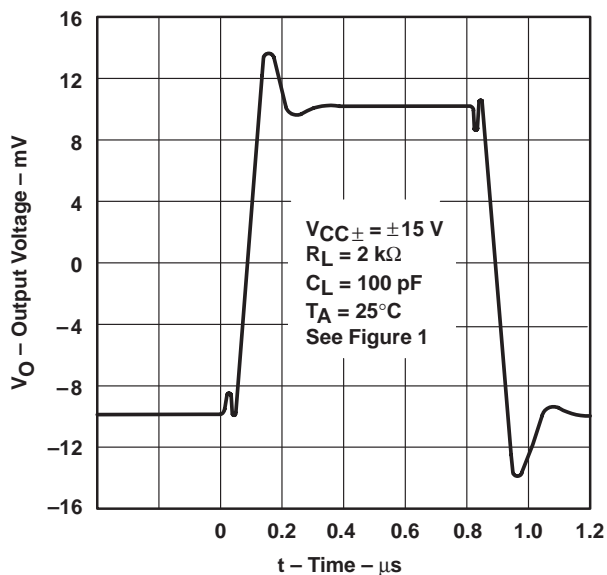


Figure 79

VOLTAGE-FOLLOWER  
 LARGE-SIGNAL  
 PULSE RESPONSE

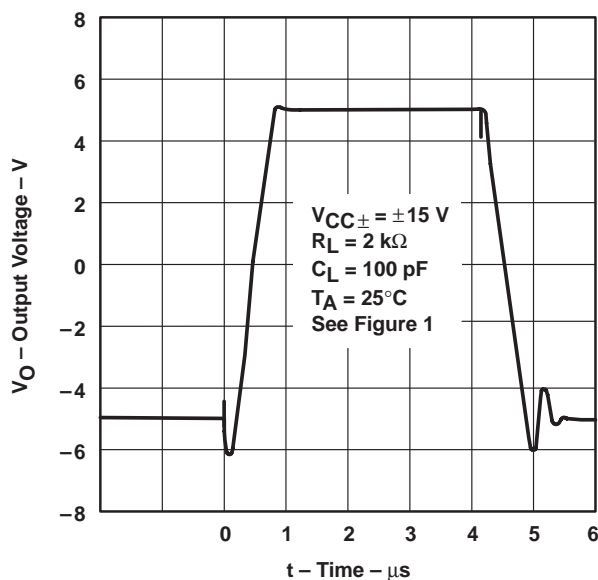


Figure 80

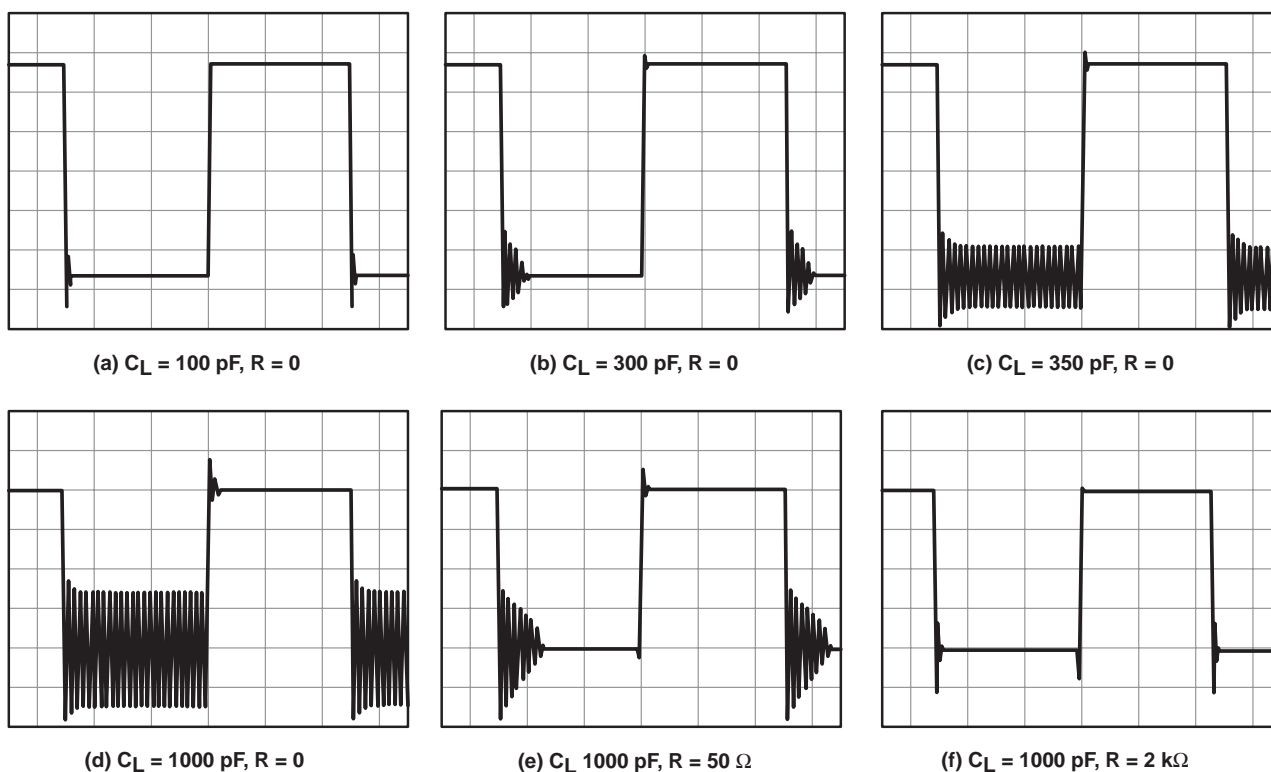
**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

SLOS178 – FEBRUARY 1997

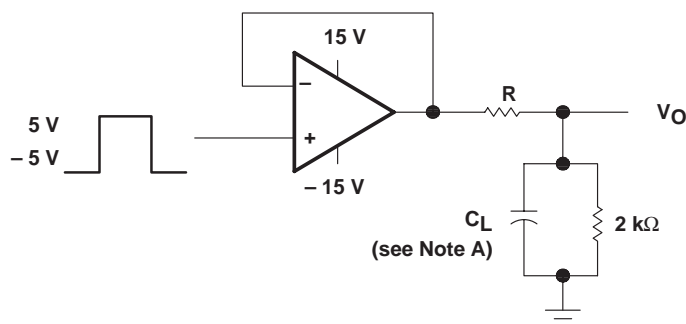
**APPLICATION INFORMATION**

**output characteristics**

All operating characteristics (except bandwidth and phase margin) are specified with 100-pF load capacitance. The TL05x and TL05xA drive higher capacitive loads; however, as the load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation. The value of the load capacitance at which oscillation occurs varies with production lots. If an application appears to be sensitive to oscillation due to load capacitance, adding a small resistance in series with the load should alleviate the problem. Capacitive loads of 1000 pF and larger may be driven if enough resistance is added in series with the output (see Figure 81 and Figure 82).



**Figure 81. Effect of Capacitive Loads**



NOTE A:  $C_L$  includes fixture capacitance.

**Figure 82. Test Circuit for Output Characteristics**

APPLICATION INFORMATION

input characteristics

The TL05x and TL05xA are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction.

Because of the extremely high input impedance and resulting low bias current requirements, the TL05x and TL05xA are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause degradation in system performance. It is good practice to include guard rings around inputs (see Figure 83). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input.

Unused amplifiers should be connected as grounded unity-gain followers to avoid possible oscillation.

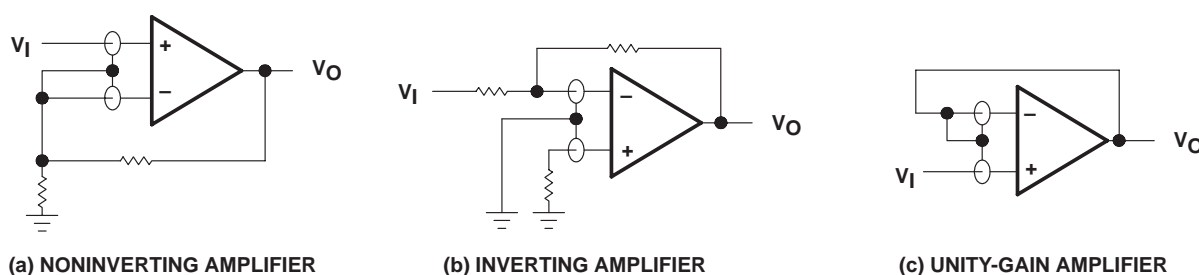


Figure 83. Use of Guard Rings

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TL05x and TL05xA result in a very low current noise. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 kΩ.

# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## APPLICATION INFORMATION

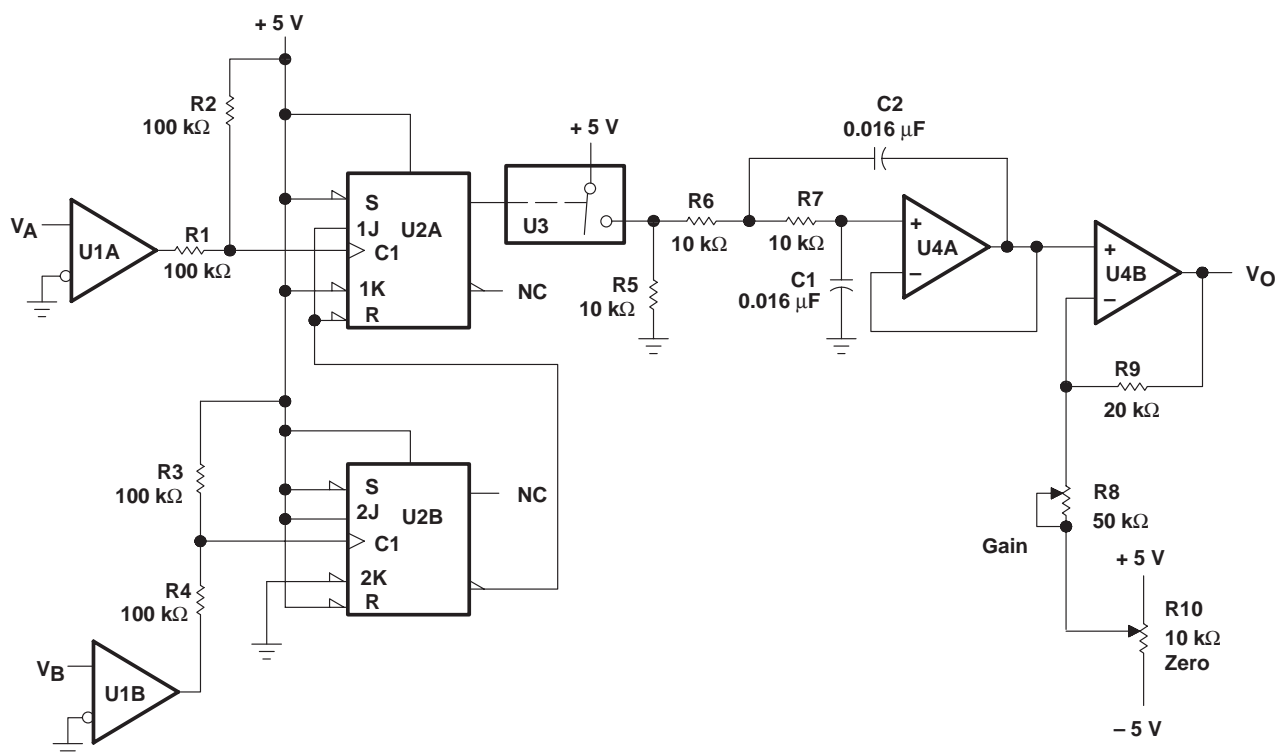
### phase meter

The phase meter in Figure 84 produces an output voltage of 10 mV per degree of phase delay between the two input signals  $V_A$  and  $V_B$ . The reference signal  $V_A$  must be the same frequency as  $V_B$ . The TLC3702 comparators (U1) convert these two input sine waves into  $\pm 5$ -V square waves. Then R1 and R4 provide level shifting prior to the SN74HC109 dual J-K flip flops.

Flip-flop U2B is connected as a toggle flip-flop and generates a square wave at half the frequency of  $V_B$ . Flip-flop U2A also produces a square wave at half the input frequency. The pulse duration of U2A varies from zero to half the period, where zero corresponds to zero phase delay between  $V_A$  and  $V_B$  and half the period corresponds to  $V_B$  lagging  $V_A$  by 360 degrees.

The output pulse from U2A causes the TLC4066 (U3) switch to charge the TL05x (U4) integrator capacitors C1 and C2. As the phase delay approaches 360 degrees, the output of U4A approximates a square wave and U2A has an output of almost 2.5 V. U4B acts as a noninverting amplifier with a gain of 1.44 in order to scale the 0- to 2.5-V integrator output to a 0- to 3.6-V output range.

R8 and R10 provide output gain and zero-level calibration. This circuit operates over a 100-Hz to 10-kHz frequency range.



NOTE A: U1 = TLC3702;  $V_{CC\pm} = \pm 5$  V  
 U2 = SN74HC109  
 U3 = TLC4066  
 U4, U5 = TL05x;  $V_{CC\pm} = \pm 5$  V

Figure 84. Phase Meter

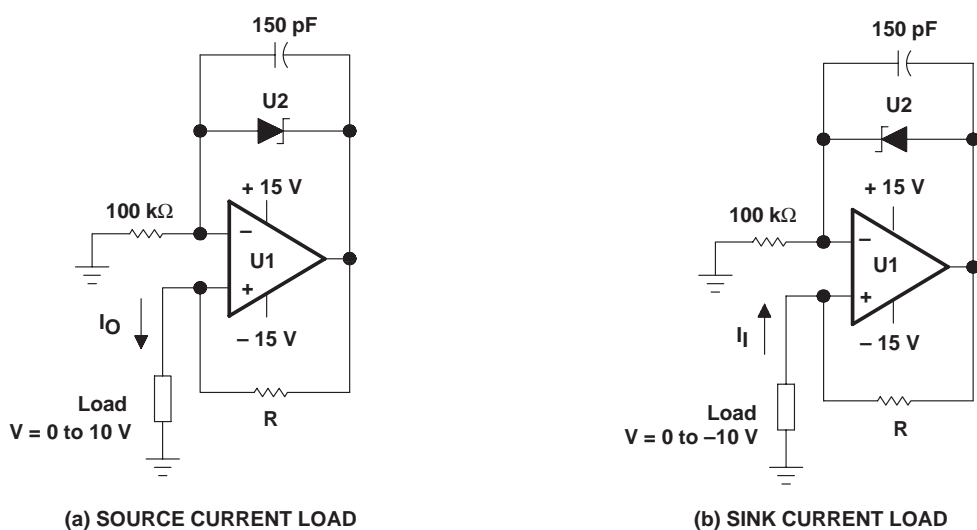


**APPLICATION INFORMATION**

**precision constant-current source over temperature**

A precision current source (see Figure 85) benefits from the high input impedance and stability of Texas Instruments enhanced-JFET process. A low-current shunt regulator maintains 2.5 V between the inverting input and the output of the TL05x. The negative feedback then forces 2.5 V across the current setting resistor R; therefore, the current to the load is simply 2.5 V divided by R.

Possible choices for the shunt regulator include the LT1004, LT1009, and LM385. If the regulator's cathode connects to the operational amplifier output, this circuit sources load current. Similarly, if the cathode connects to the inverting input, the circuit sinks current from the load. To minimize output current change with temperature, R should be a metal film resistor with a low temperature coefficient. Also, this circuit must be operated with split-voltage supplies.



NOTE B: U1 = 1/2 TL05x  
 U2 = LM385, LT1004, or LT1009 voltage reference  
 $I = \frac{2.5 \text{ V}}{R}$ , R = Low temperature coefficient metal film resistor

**Figure 85. Precision Constant-Current Source**

# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

## APPLICATION INFORMATION

### instrumentation amplifier with adjustable gain/null

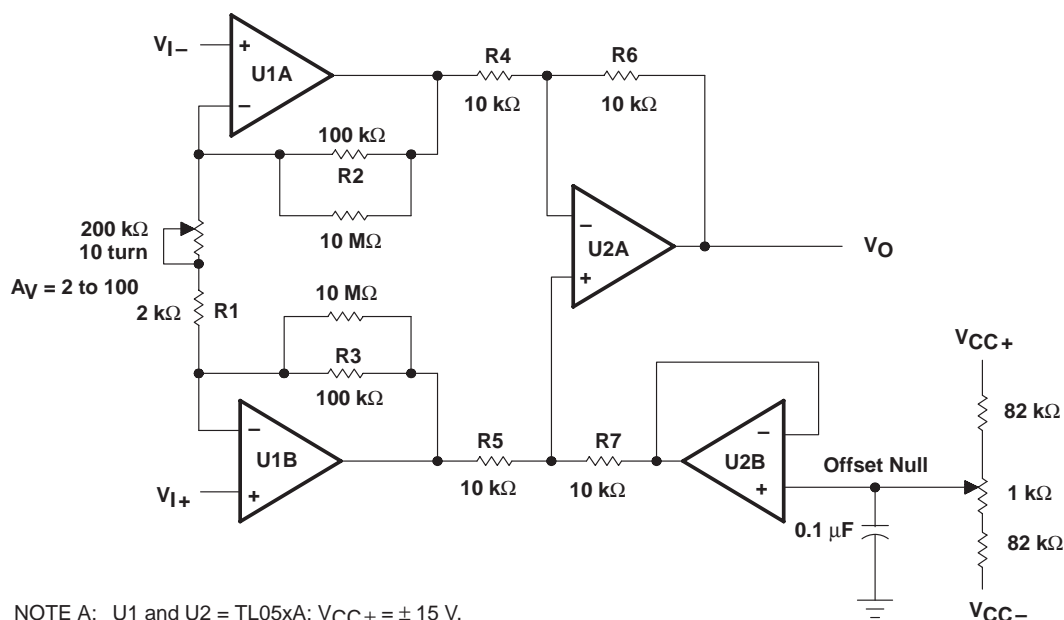
The instrumentation amplifier in Figure 86 benefits greatly from the high input impedance and stable input offset voltage of the TL05xA. Amplifiers U1A, U1B, and U2A form the actual instrumentation amplifier, while U2B provides offset null. Potentiometer R1 provides gain adjust. With  $R1 = 2\text{ k}\Omega$ , the circuit gain equals 100, while with  $R1 = 200\text{ k}\Omega$ , the circuit gain equals two. The following equation shows the instrumentation amplifier gain as a function of  $R1$ :

$$A_V = 1 + \left( \frac{R2 + R3}{R1} \right)$$

Readjusting the offset null is necessary whenever the circuit gain is changed. If U2B is needed for another application,  $R7$  can be terminated at ground. The low input offset voltage of the TL05xA minimizes the dc error of the circuit. For best matching, all resistors should be one percent tolerance. The matching between  $R4$ ,  $R5$ ,  $R6$ , and  $R7$  controls the CMRR of this application.

The following equation shows the output voltages when the input voltage equals zero. This dc error can be nulled by adjusting the offset null potentiometer; however, any change in offset voltage over time or temperature also creates an error. To calculate the error from changes in offset, consider the three offset components in the equation as delta offsets rather than initial offsets. The improved stability of Texas Instruments enhanced JFETs minimizes the error resulting from change in input offset voltage with time. Assuming  $V_I$  equals zero,  $V_O$  can be shown as a function of the offset voltage:

$$V_O = V_{IO2} \left[ \left( 1 + \frac{R3}{R1} \right) \left( \frac{R7}{R5 + R7} \right) \left( 1 + \frac{R6}{R4} \right) + \frac{R2}{R1} \left( \frac{R6}{R4} \right) \right] - V_{IO1} \left[ \frac{R3}{R1} \left( \frac{R7}{R5 + R7} \right) \left( 1 + \frac{R6}{R4} \right) + \frac{R6}{R4} \left( 1 + \frac{R2}{R1} \right) \right] + V_{IO3} \left( 1 + \frac{R6}{R4} \right)$$



NOTE A: U1 and U2 = TL05xA;  $V_{CC\pm} = \pm 15\text{ V}$ .

Figure 86. Instrumentation Amplifier

APPLICATION INFORMATION

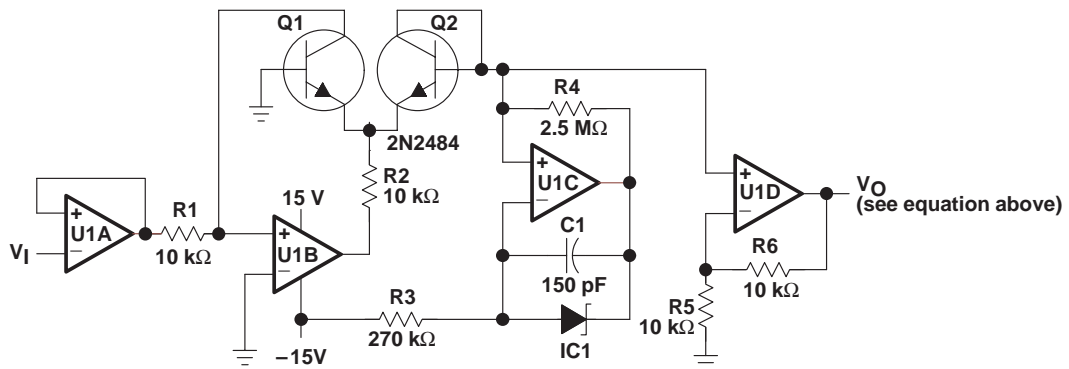
high input impedance log amplifier

The low input offset voltage and high input impedance of the TL05xA creates a precision log amplifier (see Figure 87). IC1 is a 2.5-V, low-current precision, shunt regulator. Transistors Q1 and Q2 must be a closely matched NPN pair. For best performance over temperature, R4 should be a metal film resistor with a low temperature coefficient.

In this circuit, U1A serves as a high-impedance unity-gain buffer. Amplifier U1B converts the input voltage to a current through R1 and Q1. Amplifier U1C, IC1, and R4 form a 1-μA temperature-stable current source that sets the base-emitter voltage of Q2. U1D amplifies the difference between the base-emitter voltage of Q1 and Q2 (see Figure 88). The output voltage is given by the following equation:

$$V_O = -\left[1 + \frac{R_6}{R_5}\right] \frac{kT}{q} \left[ \ln \frac{V_I}{(R_1 \times 1 \times 10^{-6})} \right]$$

where  $k = 1.38 \times 10^{-23}$ ,  $q = 1.602 \times 10^{-19}$ , and T is in degrees kelvin.



NOTE A: U1A through U1D = TL05xA. IC1 = LM385, LT1004, or LT1009 voltage reference.

Figure 87. Log Amplifier

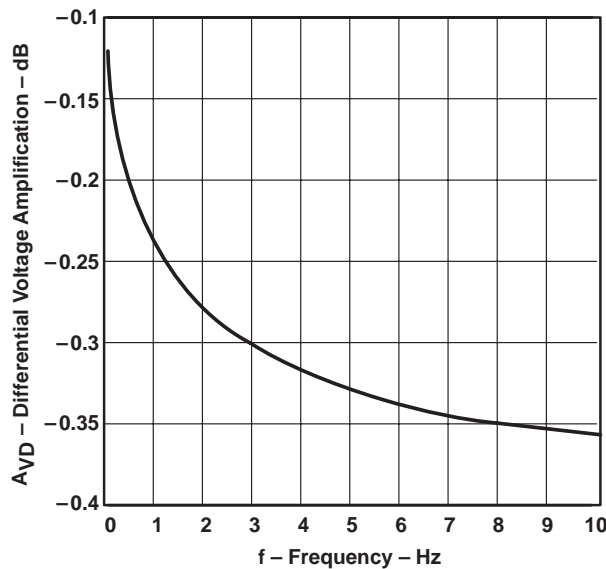


Figure 88. Output Voltage vs Input Voltage for Log Amplifier

# TL05x, TL05xA, TL05xY ENHANCED-JFET LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS178 – FEBRUARY 1997

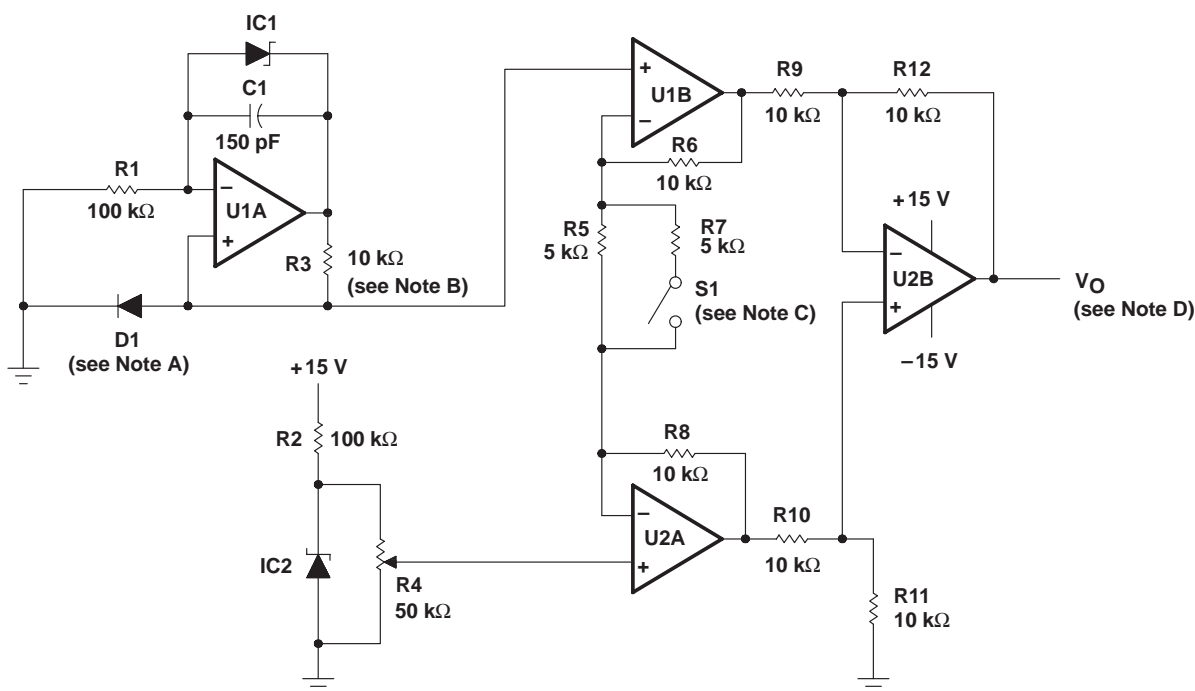
## APPLICATION INFORMATION

### analog thermometer

By combining a current source that does not vary over temperature with an instrumentation amplifier, a precise analog thermometer can be built (see Figure 89). Amplifier U1A and IC1 establish a constant current through the temperature-sensing diode D1. For this section of the circuit to operate correctly, the TL05x must use split supplies and R3 must be a metal-film resistor with a low temperature coefficient.

The temperature-sensitive voltage from the diode is compared to a temperature-stable voltage reference set by IC2. R4 should be adjusted to provide the correct output voltage when the diode is at a known temperature. Although this potentiometer resistance varies with temperature, the divider ratio of the potentiometer remains constant.

Amplifiers U1B, U2A, and U2B form the instrumentation amplifier that converts the difference between the diode and reference voltage to a voltage proportional to the temperature. With switch S1 closed, the amplifier gain equals 5 and the output voltage is proportional to temperature in degrees Celsius. With S1 open, the amplifier gain is 9 and the output is proportional to temperature in degrees Fahrenheit. Every time that S1 is changed, R4 must be recalibrated. By setting S1 correctly, the output voltage equals 10 mV per degree (C or F).



- NOTES:
- A. Temperature-sensing diode  $\approx (-2 \text{ mV}/^\circ\text{C})$
  - B. Metal-film resistor (low temperature coefficient)
  - C. Switch open for  $^\circ\text{F}$  and closed for  $^\circ\text{C}$
  - D.  $V_O \propto$  temperature; 10 mV/ $^\circ\text{C}$  or 10 mV/ $^\circ\text{F}$
  - E. U1, U2 = TL05x. IC1, IC2 = LM385, LT1004, or LT1009 voltage reference

Figure 89. Analog Thermometer

## APPLICATION INFORMATION

### voltage-ratio-to-dB converter

The application in Figure 90 measures the amplitude ratio of two signals and then converts the ratio to decibels (see Figure 91). The output voltage provides a resolution of 100 mV/dB. The two inputs can be either dc or sinusoidal ac signals. When using ac signals, both signals should be the same frequency or output glitches will occur. For measuring two input signals of different frequencies, extra filtering should be added after the rectifiers.

The circuit contains three low-offset TL05xA devices. Two of these devices provide the rectification and logarithmic conversion of the inputs. The third TL05xA forms an instrumentation amplifier. The stage performing the logarithmic conversion also requires two well-matched npn transistors.

The input signal first passes through a high impedance unity-gain buffer U1A (U2A). Then U1B (U2B) rectifies the input signal at a gain of 0.5, and U1C (U2C) provides a noninverting gain of 2 so that the system gain is still one. U1D (U2D), R6 (R13), and Q1 (Q2) perform the logarithmic conversion of the rectified input signal. The instrumentation amplifier formed by U3A, U3B, U3D scales the difference of the two logarithmic voltages by a gain of 33.6. As a result, the output voltage equals 100 mV/dB. The 1-kΩ potentiometer on the input of U3C calibrates the zero dB reference level. The following equations are used to derive the relationship between the input voltage ratio expressed in decibels and the output voltage.

$$X \text{ dB} = 20 \log \left[ \frac{V_A}{V_B} \right] = 20 \left[ \frac{\ln(V_A) - \ln(V_B)}{\ln(10)} \right]$$

$$X \text{ dB} = 8.686 \left[ \ln(V_A) - \ln(V_B) \right]$$

$$V_{BE(Q1)} = \frac{kT}{q} \ln \left[ \frac{V_A}{R \times I_S} \right] \quad V_{BE(Q2)} = \frac{kT}{q} \ln \left[ \frac{V_B}{R \times I_S} \right]$$

$$\Delta V_{BE} = V_{BE(Q1)} - V_{BE(Q2)} = \frac{kT}{q} \left[ \ln(V_A) - \ln(V_B) \right]$$

$$X \text{ dB} = \frac{8.686}{kT/q} \left[ V_{BE(Q1)} - V_{BE(Q2)} \right] = 336 \left[ V_{BE(Q1)} - V_{BE(Q2)} \right] \text{ at } 25^\circ\text{C}$$

where

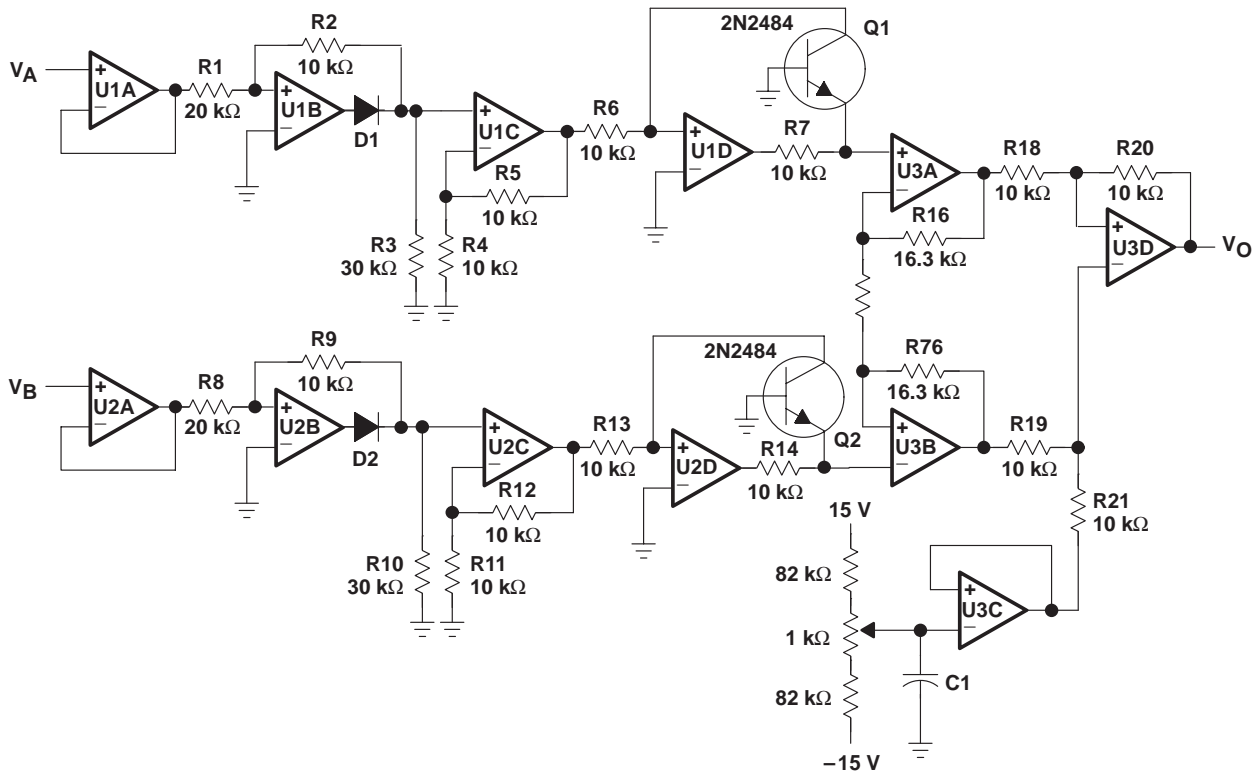
$$k = 1.38 \times 10^{-23}, \quad q = 1.602 \times 10^{-19}, \quad \text{and } T \text{ is in kelvins.}$$

This would give a resolution of 1 V/dB. Therefore, the gain of the instrumentation amplifier is set at 33.6 to obtain 100 mV/dB.

**TL05x, TL05xA, TL05xY**  
**ENHANCED-JFET LOW-OFFSET**  
**OPERATIONAL AMPLIFIERS**

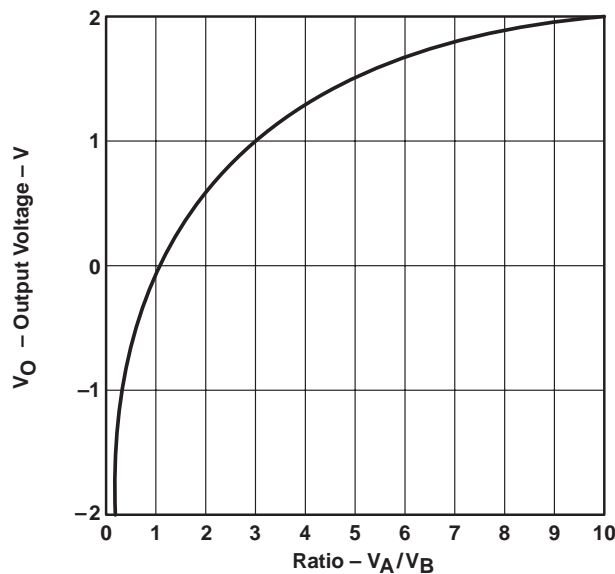
SLOS178 – FEBRUARY 1997

**APPLICATION INFORMATION**



NOTE A: U1A through U3D = TL05xA,  $V_{CC\pm} = \pm 15$  V. D1 and D2 = 1N914.

**Figure 90. Voltage-Ratio-to-dB Converter**



**Figure 91. Output Voltage vs the Ratio of the Input Voltages for Voltage-to-dB Converter**



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APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 5) and subcircuit Figure 92 are generated using the TL05x typical electrical and operating characteristics at  $T_A = 25^\circ\text{C}$ . Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 5: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

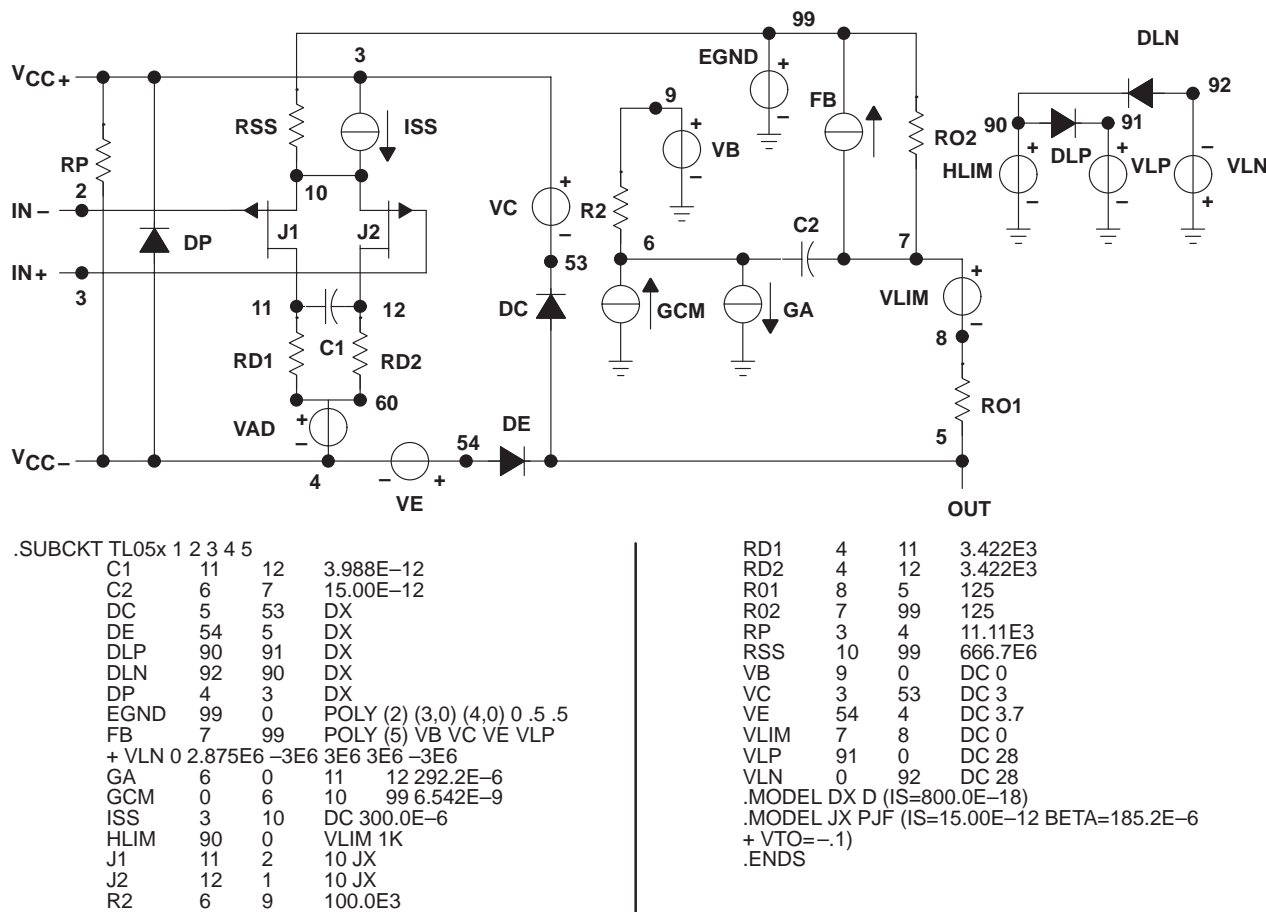


Figure 92. Boyle Macromodel and Subcircuit

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